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(54) **MATERIALS FOR ORGANIC ELECTROLUMINESCENT DEVICES**

(75) Inventors: **Holger Heil**, Darmstadt (DE); **Philipp Stoessel**, Frankfurt am Main (DE); **Amir Parham**, Frankfurt (DE); **Horst Vestweber**, Gilserberg-Wintercheid (DE)

(73) Assignee: **Merck Patent GmbH** (DE)

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Mar. 2, 2006 (DE) 10 2006 009 630

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257/E51.032; 585/27

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585/27

See application file for complete search history.

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Primary Examiner — Gregory Clark

(74) Attorney, Agent, or Firm — Drinker Biddle & Reath LLP

(57) **ABSTRACT**

The present invention relates to anthracene derivatives, to the use thereof in organic electroluminescent devices, and to organic electroluminescent devices comprising these compounds.

20 Claims, No Drawings

**MATERIALS FOR ORGANIC
ELECTROLUMINESCENT DEVICES**

RELATED APPLICATIONS

This application is a national stage application (under 35 U.S.C. §371) of PCT/EP2006/011029, filed Nov. 17, 2006, which claims benefit of German application 10 2005 058 557.4, filed Dec. 8, 2005, and German application 10 2006 009 630.4, filed Mar. 2, 2006.

The present invention describes novel anthracene derivatives, the use of these compounds in organic electroluminescent devices, and organic electroluminescent devices comprising these compounds.

Organic semiconductors are used as functional materials in a number of applications of different types which can be ascribed to the electronics industry in the broadest sense. The general structure of organic electroluminescent devices which are capable of the emission of light in the visible spectral region is described, for example, in U.S. Pat. No. 4,539,507, U.S. Pat. No. 5,151,629, EP 0676461 and WO 98/27136.

However, these devices still have considerable problems which require urgent improvement for use in high-quality full-colour displays:

1. The compounds used do not have adequate thermal stability and do not have a sufficiently high glass-transition temperature.
2. The compounds used are not sufficiently soluble in organic solvents, which makes their purification during preparation and cleaning of the vapour-deposition units (for example the shadow masks) more difficult.
3. The hole and electron stability (redox stability) of the compounds used to date is still inadequate.

The closest prior art which may be mentioned is the use of various condensed aromatic compounds, in particular anthracene or pyrene derivatives, as host materials, in particular for blue-emitting electroluminescent devices. The host material known in accordance with the prior art is 9,10-bis (2-naphthyl)anthracene (U.S. Pat. No. 5,935,721). Further anthracene derivatives which are suitable as host materials are described, for example, in WO 01/076323, in WO 01/021729, in WO 04/013073, in WO 04/018588, in WO 03/087023 or in WO 04/018587. Host materials based on aryl-substituted pyrenes and chrysenes are described in WO 04/016575, which in principle also encompasses corresponding anthracene and phenanthrene derivatives. WO 03/095445 and CN 1362464 describe 9,10-bis(1-naphthyl)anthracene derivatives for use in OLEDs.

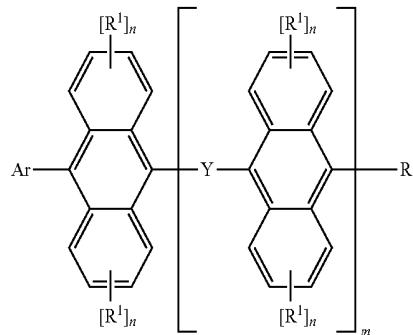
The object of the present invention was to provide compounds having improved properties, in particular improved host materials and improved blue and green emitters.

Surprisingly, it has been found that organic electroluminescent devices which comprise certain anthracene derivatives which are substituted by trialkylsilyl groups have significant improvements over the prior art. These compounds have high thermal stability, a high glass-transition temperature, high redox stability and good solubility in organic solvents. The present invention therefore relates to these compounds and to the use thereof in OLEDs.

The invention relates to silyl-substituted compounds of the formula (1)

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Formula (1)



where the following applies to the symbols and indices used:

Ar is a 1-naphthyl group or a 9-anthryl group, in which one or two carbon atoms may be replaced by N and which may be substituted by one or more radicals R¹ and/or which may be substituted by one or more radicals N(Ar¹)₂, where the two radicals Ar¹ may also be connected to one another by a single bond or an O, S, N(R¹) or C(R¹)₂ group;

R is an aromatic or heteroaromatic ring system having 5 to 40 aromatic ring atoms, which may be substituted by one or more radicals R¹, or an N(Ar¹)₂ group, where the two radicals Ar¹ may also be connected to one another by a single bond or an O, S, N(R¹) or C(R¹)₂ group;

Ar¹ is on each occurrence, identically or differently, an aromatic or heteroaromatic ring system having 5 to 40 aromatic ring atoms, which may be substituted by one or more radicals R¹;

Y is on each occurrence, identically or differently, a divalent group containing 1 to 40 C atoms or —O—, —S—, —NR¹—, —P(=O)R¹— or a single bond;

R¹ is, identically or differently on each occurrence, Si(R²)₃, F, Cl, Br, I, CN, N(R³)₂, NO₂, a straight-chain alkyl, alkoxy or thioalkoxy group having 1 to 40 C atoms or a branched or cyclic alkyl, alkoxy or thioalkoxy group having 3 to 40 C atoms, each of which may be substituted by one or more radicals R³, where one or more non-adjacent CH₂ groups may be replaced by —R³C=CR³—, —C≡C—, Si(R³)₂, Ge(R³)₂, Sn(R³)₂, C=O, C=S, C=Se, C=NR³, —O—, —S—, —N(R³)— or —CONR³— and where one or more H atoms may be replaced by F, Cl, Br, I, CN or NO₂, or an aryl or heteroaryl group having 5 to 24 aromatic ring atoms, which may be substituted by one or more radicals R³, or an aryloxy or heteroaryloxy group having 5 to 24 aromatic ring atoms, which may be substituted by one or more radicals R³, or a combination of two, three, four or five of these systems; two or more adjacent substituents R¹ here may also form a mono- or polycyclic, aliphatic ring system with one another;

R² is on each occurrence, identically or differently, a straight-chain alkyl group having 1 to 40 C atoms or a branched or cyclic alkyl group having 3 to 40 C atoms, in each of which one or more non-adjacent CH₂ groups which are not bonded directly to the silicon may be replaced by —R³C=CR³—, —C≡C—, Si(R³)₂, Ge(R³)₂, Sn(R³)₂, C=O, C=S, C=Se, C=NR³, —O—, —S—, —N(R³)— or —CONR³— and in each of which one or more H atoms may be replaced by F, Cl, Br, I, CN or NO₂, and which may also be substituted by an aryl or heteroaryl group having 5 to 24 aromatic ring atoms, which may be substituted by one or more radicals R³, or by an aryloxy or heteroaryloxy group having 5 to 24 aromatic ring atoms, which may be

substituted by one or more radicals R^3 ; two or more substituents R^2 here may also form a mono- or polycyclic ring system with one another;

R^3 is on each occurrence, identically or differently, H or a hydrocarbon radical having 1 to 20 C atoms, which may be aliphatic or aromatic or a combination of aliphatic and aromatic and which may also be substituted by F; two or more radicals R^3 here may also form a mono- or polycyclic, aliphatic or aromatic ring system with one another;

n is, identically or differently on each occurrence, 0, 1, 2, 3 or 4;

m is 0, 1, 2, 3, 4 or 5;

characterised in that at least one radical R^1 which represents an $Si(R^2)_3$ group is present in the molecule.

For the purposes of this invention, an aryl group or a heteroaryl group is taken to mean an aromatic group or heteroaromatic group respectively having a common aromatic π -electron system. For the purposes of this invention, this may be a simple homo- or heterocycle, for example benzene, pyridine, thiophene, etc., or it may be a condensed aryl or heteroaryl group in which at least two aromatic or heteroaromatic rings, for example benzene rings, are "fused" to one another, i.e. are condensed onto one another by anellation, i.e. have at least one common edge and thus also a common aromatic π -electron system. These aryl or heteroaryl groups may be substituted or unsubstituted; any substituents present may likewise form further ring systems. Thus, for example, systems such as naphthalene, anthracene, phenanthrene, pyrene, etc., are regarded as aryl groups and quinoline, acridine, benzothiophene, carbazole, etc., are regarded as heteroaryl groups for the purposes of this invention, while, for example, biphenyl, fluorene, spirobifluorene, etc., do not represent aryl groups since they involve separate aromatic electron systems.

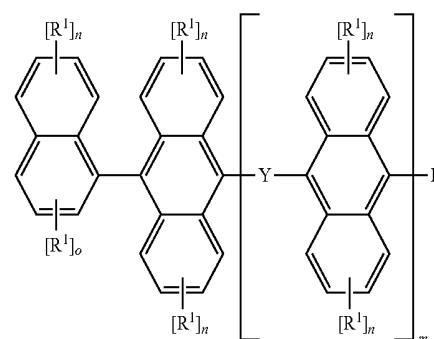
For the purposes of this invention, an aromatic ring system contains 6 to 40 C atoms in the ring system. For the purposes of this invention, a heteroaromatic ring system contains 2 to 40 C atoms and at least one heteroatom in the ring system, with the proviso that the sum of C atoms and heteroatoms is at least 5. The heteroatoms are preferably selected from N, and/or S. For the purposes of this invention, an aromatic or heteroaromatic ring system is intended to be taken to mean a system which does not necessarily contain only aryl or heteroaryl groups, but instead in which a plurality of aryl or heteroaryl groups may also be interrupted by a short non-aromatic unit (less than 10% of the atoms other than H, preferably less than 5% of the atoms other than H), such as, for example, an sp^3 -hybridised C, N or O atom. Thus, for example, systems such as 9,9'-spirobifluorene, fluorene, 9,9-diarylfluorene, triarylamine, diaryl ether, etc., are also intended to be taken to mean aromatic ring systems for the purposes of this invention. Part of the aromatic or heteroaromatic ring system may also be a condensed group here.

For the purposes of the present invention, a C_1 - to C_{40} -alkyl group, in which, in addition, individual H atoms or CH_2 groups may be substituted by the above-mentioned groups, is particularly preferably taken to mean the radicals methyl, ethyl, n-propyl, i-propyl, n-butyl, i-butyl, s-butyl, t-butyl, 2-methylbutyl, n-pentyl, s-pentyl, cyclopentyl, n-hexyl, cyclohexyl, n-heptyl, cycloheptyl, n-octyl, cyclooctyl, 2-ethylhexyl, trifluoromethyl, pentafluoroethyl, 2,2,2-trifluoroethyl, ethenyl, propenyl, butenyl, pentenyl, cyclopentenyl, hexenyl, cyclohexenyl, heptenyl, cycloheptenyl, octenyl, cyclooctenyl, ethynyl, propynyl, butynyl, pentynyl, hexynyl or octynyl. A C_1 - to C_{40} -alkoxy group is particularly preferably taken to mean methoxy, ethoxy, n-propoxy, i-propoxy, n-butoxy, i-butoxy, s-butoxy, t-butoxy or 2-methylbutoxy. An

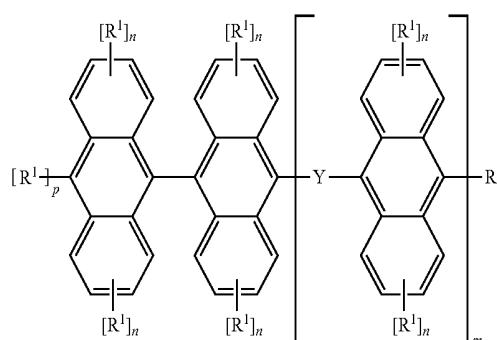
aromatic or heteroaromatic ring system having 1 to 30 aromatic ring atoms, which may also in each case be substituted by the above-mentioned radicals R^1 or R^2 and which may be linked to the aromatic or heteroaromatic ring system via any desired positions, is taken to mean, in particular, groups derived from benzene, naphthalene, anthracene, phenanthrene, pyrene, chrysene, perylene, fluoranthene, tetracene, pentacene, benzopyrene, biphenyl, biphenylene, terphenyl, terphenylene, fluorene, spirobifluorene, truxene, isotruxene, dihydrophenanthrene, dihydropyrene, tetrahydropyrene, cis- or trans-indenofluorene, furan, benzofuran, isobenzofuran, dibenzofuran, thiophene, benzothiophene, isobenzothiophene, dibenzothiophene, pyrrole, indole, isoindole, carbazole, pyridine, quinoline, isoquinoline, acridine, phenanthridine, benzo-5,6-quinoline, benzo-6,7-quinoline, benzo-7,8-quinoline, phenothiazine, phenoxazine, pyrazole, indazole, imidazole, benzimidazole, naphthimidazole, phenanthrimidazole, pyridimidazole, pyrazimidazole, quinoxalinimidazole, oxazole, benzoxazole, naphthoxazole, anthroxazole, phenanthroxazole, isoxazole, 1,2-thiazole, 1,3-thiazole, benzothiazole, pyridazine, benzo pyridazine, pyrimidine, benzopyrimidine, quinoxaline, pyrazine, phenazine, naphthyridine, azacarbazole, benzocarboline, phenanthroline, 1,2,3-triazole, 1,2,4-triazole, benzotriazole, 1,2,3-oxadiazole, 1,2,4-oxadiazole, 1,2,5-oxadiazole, 1,3,4-oxadiazole, 1,2,3-thiadiazole, 1,2,4-thiadiazole, 1,2,5-thiadiazole, 1,3,4-thiadiazole, 1,3,5-triazine, 1,2,4-triazine, 1,2,3-triazine, tetrazole, 1,2,4,5-tetrazine, 1,2,3,4-tetrazine, 1,2,3,5-tetrazine, purine, pteridine, indolizine and benzothiadiazole.

Preference is given to compounds of the formula (1) in which the symbol Ar stands for a 1-naphthyl group, a 9-anthryl group, a 1-, 4-, 5- or 8-isoquinolyl group or a 4- or 5-quinolyl group. Particular preference is given to compounds of the formula (1) in which the symbol Ar stands for a 1-naphthyl group or a 9-anthryl group. Very particular preference is given to the compounds of the formulae (1a) to (1d)

Formula (1a)



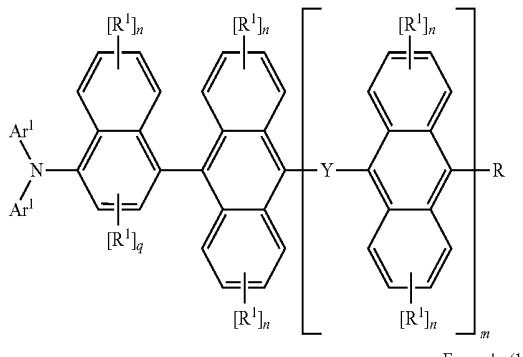
Formula (1b)



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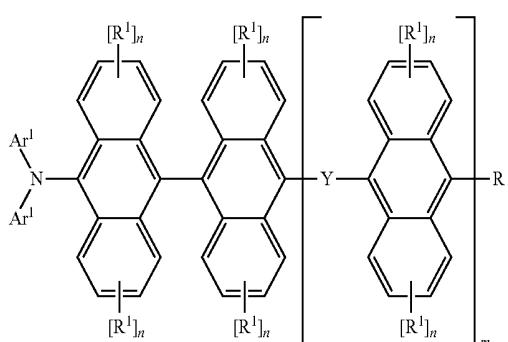
-continued

Formula (1c)



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Formula (1d)



where R^1 , Ar^1 , R^1 , Y , m and n have the meaning defined above, where the two radicals Ar^1 may also be connected to one another by a single bond or an O, S, $N(R^1)$ or $C(R^1)_2$ group, and furthermore the following applies:

o is 0, 1, 2 or 3;

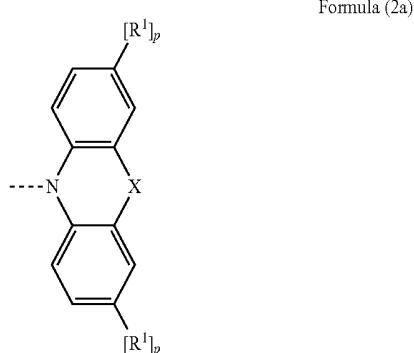
p is 0 or 1;

q is 0, 1 or 2;

characterised in that at least one radical R^1 which stands for an $Si(R^2)_3$ group is present.

In compounds of the formula (1b), the index p is preferably 1, i.e. a further substituent other than hydrogen is preferably bonded to the anthryl group in the 10-position.

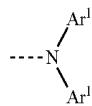
Preference is furthermore given to compounds of the formulae (1) and (1a) to (1d) in which the symbol R stands for an aromatic or heteroaromatic ring system having 6 to 24 aromatic ring atoms, which may be substituted by one or more radicals R^1 , or in which the symbol R stands for a group of the formula (2a) or (2b)



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-continued

Formula (2b)



where R^1 and p have the meaning indicated above, and furthermore the following applies:

10 X stands for a single bond, O, S, $N(R^1)$ or $C(R^1)_2$;
 Ar^1 is, identically or differently on each occurrence, an aryl or heteroaryl group having 5 to 20 aromatic ring atoms, which may be substituted by one or more radicals R^1 , preferably an aryl or heteroaryl group having 6 to 14 aromatic ring atoms, which may be substituted by one or more radicals R^1 , particularly preferably phenyl, 1-naphthyl or 2-naphthyl, each of which may be substituted by one or more radicals R^1 .

20 If a substituent on the Ar group stands for an $N(Ar^1)_2$ group, this substituent is also preferably selected from the formulae (2a) and (2b) indicated above.

If the symbol R stands for an aromatic or heteroaromatic ring system, it preferably stands for an aromatic or heteroaromatic ring system having 9 to 24 aromatic ring atoms, which may be substituted by one or more radicals R^1 . Particular preference is given to compounds of the formula (1) in which the symbol R stands for a condensed aryl or heteroaryl group having 10 to 16 aromatic ring atoms or for an aromatic, 25 optionally bridged biaryl group, each of which may be substituted by one or more radicals R^1 . Very particular preference is given to compounds of the formula (1) in which the symbol R , if it stands for an aromatic or heteroaromatic ring system, stands, identically or differently on each occurrence, for a 1-naphthyl, 2-naphthyl, 9-anthryl, 2-phenanthrenyl, 9-phenanthrenyl, quinolinyl, isoquinolinyl, ortho-, meta- or para-biphenyl, 2-fluorenyl or 2-spirobifluorenyl group, each of which may be substituted by one or more radicals R^1 , in particular for 1-naphthyl, which may be substituted by one or 30 more radicals R^1 .

35 Preference is furthermore given to compounds of the formulae (1) and (1a) to (1d) which, if the group R stands for an aromatic or heteroaromatic ring system, have hindered rotation about the anthracene- R bond. For the purposes of this 40 invention, hindered rotation is taken to mean a rotation barrier of at least 80 kJ/mol, preferably at least 100 kJ/mol, particularly preferably at least 120 kJ/mol, at room temperature. This rotation barrier can be determined experimentally by temperature-dependent NMR measurements. If the compound of the formula (1) or (1a) or (1b) exhibits atropisomerism about one or more bonds, the invention in each case also relates to 45 OLEDs comprising the corresponding isolated or enriched atropisomers. This relates both to enantiomers and also to diastereomers. Hindered rotation about the anthracene- R bond is achieved if the group R has at least one organic 50 substituent in the ortho-position and/or if the group R is, for example, a 1-naphthyl group which contains peri-hydrogen atoms.

55 Both compounds of the formula (1) in which the two groups Ar and R are selected identically and also compounds of the formula (1) in which the groups Ar and R are different are in accordance with the invention.

Preference is furthermore given to compounds of the formulae (1) and (1a) to (1d) in which the symbol R^1 , identically 60 or differently on each occurrence, stands for $Si(R^2)_3$, F, a straight-chain alkyl or alkoxy group having 1 to 6 C atoms or a branched or cyclic alkyl or alkoxy group having 3 to 10 C

atoms, in each of which one or more CH_2 groups may be replaced by $-\text{R}^3\text{C}=\text{CR}^3-$, $\text{Si}(\text{R}^3)_2$, $-\text{O}-$, $-\text{S}-$ or $-\text{N}(\text{R}^3)-$ and in each of which one or more H atoms may be replaced by F, or an aryl or heteroaryl group having 5 to 14 aromatic ring atoms, which may be substituted by one or more radicals R^3 , or a combination of two or three of these systems; two or more radicals R^1 here may also form a mono- or polycyclic, aliphatic ring system with one another. Particularly preferred radicals R^1 are selected from the group consisting of $\text{Si}(\text{R}^2)_3$, F, straight-chain alkyl groups having 1 to 4 C atoms and branched alkyl groups having 3 to 5 C atoms, in each of which one or more H atoms may be replaced by F, or aryl or heteroaryl groups having 6 to 10 aromatic ring atoms, or a combination of two of these systems; two or more adjacent radicals R^1 here may also form a mono- or polycyclic, aliphatic ring system with one another.

Preference is furthermore given to compounds of the formulae (1) and (1a) to (1d) in which the symbol Y, identically or differently on each occurrence, represents a linear alkylene group having 1 to 10 C atoms or a branched or cyclic alkylene or alkylidene group having 3 to 10 C atoms, a divalent aromatic group having 6 to 25 C atoms, $\text{C}=\text{O}$, $-\text{O}-$, $-\text{S}-$ or a group of the formula $-\text{N}(\text{R}^1)-$ or $-\text{P}(\text{=O})\text{R}^1-$ or a single bond. Particular preference is given to compounds in which the symbol Y, identically or differently on each occurrence, represents a linear alkylene group having 1 to 4 C atoms, a branched alkylene or alkylidene group having 3 to 5 C atoms, a cyclic alkylene group having 3 to 10 C atoms, a divalent aromatic group selected from groups derived from benzene, naphthalene, biphenyl or terphenyl, or $\text{C}=\text{O}$, $-\text{N}(\text{R}^3)-$ or $-\text{P}(\text{=O})\text{R}^3-$ or a single bond.

Preference is furthermore given to compounds of the formulae (1) and (1a) to (1d) in which the index m stands for 0, 1 or 2, particularly preferably 0 or 1.

Preference is furthermore given to compounds of the formulae (1) and (1a) to (1d) in which the index n stands for 0, 1 or 2, particularly preferably 0 or 1, where at least one radical R^1 which stands for $\text{Si}(\text{R}^2)_3$ is present in the molecule. The compound of the formulae (1) and (1a) to (1d) preferably contains one, two, three or four groups of the formula $\text{Si}(\text{R}^2)_3$, particularly preferably one or two groups of the formula $\text{Si}(\text{R}^2)_3$.

The groups of the formula $\text{Si}(\text{R}^2)_3$ can be bonded in various positions of the molecule. In a preferred embodiment of the invention, at least one group of the formula $\text{Si}(\text{R}^2)_3$ is bonded to the central anthracene unit, preferably in the 2-position and/or in the 6-position of the anthracene. In a further preferred embodiment of the invention, at least one group of the formula $\text{Si}(\text{R}^2)_3$ is bonded to the group Ar. If the group Ar represents a 1-naphthyl group, the group of the formula $\text{Si}(\text{R}^2)_3$ is preferably bonded in the 4-position of the naphthyl group. If the group Ar represents a 9-anthryl group, the group of the formula $\text{Si}(\text{R}^2)_3$ is preferably bonded in the 10-position of the anthracene group or in the 2-position or 2,6-position if another radical R^1 is bonded in the 10-position. In still a further preferred embodiment of the invention, at least one group of the formula $\text{Si}(\text{R}^2)_3$ is bonded to the group R. If the group R represents an aryl group or a heteroaryl group, the group of the formula $\text{Si}(\text{R}^2)_3$ is preferably bonded in the para-position to the aryl group. If the group R represents a group of the formula $\text{N}(\text{Ar}^1)_2$, the group of the formula $\text{Si}(\text{R}^2)_3$ is preferably bonded to one or both groups Ar^1 in the para-position to the nitrogen.

Preferred radicals R^2 on the silyl group are selected from straight-chain alkyl groups having 1 to 10 C atoms and branched or cyclic alkyl groups having 3 to 10 C atoms, in each of which one or more non-adjacent CH_2 groups which

are not bonded directly to the silicon may be replaced by O and in each of which one or more H atoms may be replaced by F; two or more substituents R^2 here may also form a mono- or polycyclic ring system with one another. Particularly preferred radicals R^2 on the silyl group are selected from straight-chain alkyl groups having 1 to 4 C atoms or branched alkyl groups having 3 or 4 C atoms, in each of which one or more H atoms may be replaced by F. Very particularly preferred groups R^2 are methyl, CF_3 , ethyl, isopropyl and tert-butyl. Very particularly preferred $\text{Si}(\text{R}^2)_3$ groups are $\text{Si}(\text{Me})_3$, $\text{Si}(\text{Me})_2(\text{t-Bu})$, $\text{SiMe}(\text{t-Bu})_2$ and $\text{Si}(\text{i-Pr})_3$.

Preference is furthermore given to compounds of the formula (1) whose molecular weight is between 400 and 1500 g/mol, particularly preferably between 400 and 900 g/mol.

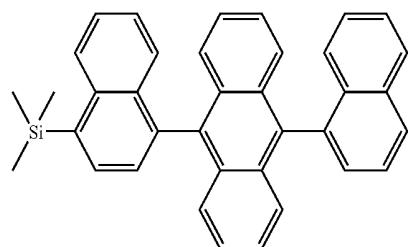
Various processes are available for the preparation of the compounds according to the invention. If the silyl group is to be introduced on the anthracene, a suitable starting compound is 2-bromoanthraquinone or 2,6-dibromoanthraquinone or the corresponding chloroanthraquinone derivative. This can in each case be reacted with a reactive organometallic reagent, for example an aryl-Grignard reagent or aryllithium reagent, and reduced in a subsequent step, for example using tin(II) chloride, giving 9,10-diarylanthracene derivatives which also carry bromine or chlorine in the 2- or 2,6-position. Metallation, for example lithiation, and reaction with a silyl halide, for example trialkylsilyl chloride, results in the corresponding silylated target compound.

If the silyl group is not to be introduced onto the central anthracene, but instead onto the aromatic Ar or R groups, it is also possible to introduce it in a first step and only then to couple the aromatic group to the anthracene in a further step. Thus, a dibromoaromatic compound can be selectively monolithiated and reacted with a silyl halide to give a bromosilyl aromatic compound. This can in turn be converted by lithiation into the corresponding boronic acid or a boronic acid derivative, which can then be coupled to dibromoanthracene or another anthracene derivative in a Suzuki coupling with palladium catalysis. Further coupling reactions between the aromatic compound and the anthracene are suitable analogously, for example the Stille coupling. If the R group represents a diarylaminogroup, a Hartwig-Buchwald coupling is suitable.

This invention furthermore relates to a process for the preparation of the compounds of the formula (1) according to the invention which carry one or more $\text{Si}(\text{R}^2)_3$ groups on the Ar or R group, by coupling a functionalised Ar or R group which is substituted by one or more $\text{Si}(\text{R}^2)_3$ groups to a corresponding anthracene derivative. The coupling is preferably a transition metal-catalysed coupling reaction, in particular a Suzuki coupling, a Stille coupling or a Hartwig-Buchwald coupling. The functionalisation of the Ar or R group here may be a boronic acid derivative for use in a Suzuki coupling. The group may be a trialkyltin derivative for use in a Stille coupling. It may be an N—H functionality for use in a Hartwig-Buchwald coupling. It may furthermore be a brominated compound if the anthracene is correspondingly substituted by a boronic acid derivative or by a trialkyltin derivative. It is surprising here that the silyl group on the Ar or R group can be employed with no damage in the metal-catalysed coupling reaction and that this does not result in side reactions.

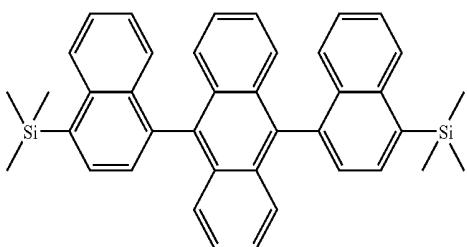
Examples of preferred compounds of the formula (1) are compounds (A1) to (A68) depicted below.

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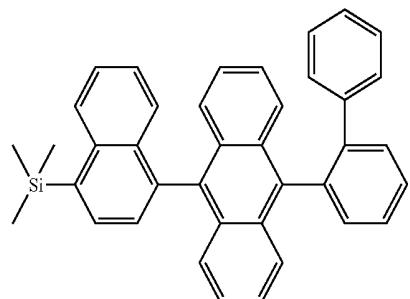


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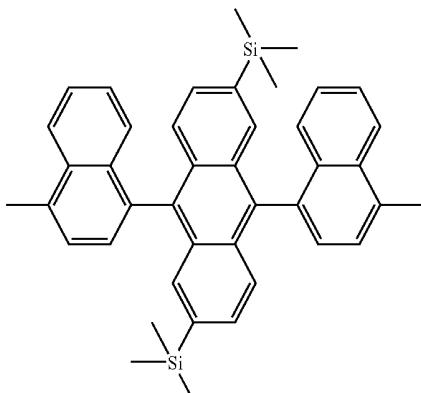
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(A2)

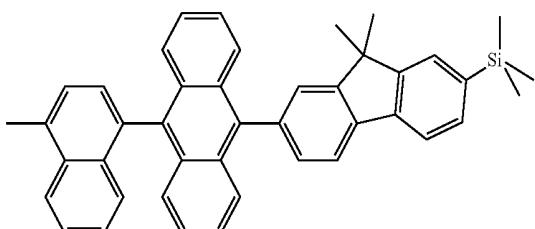
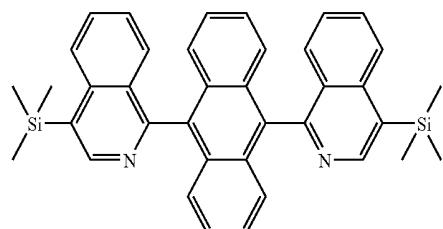


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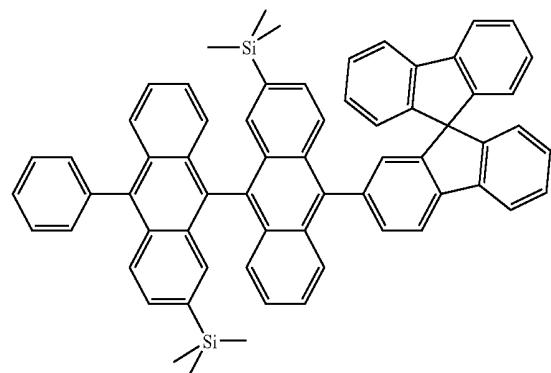
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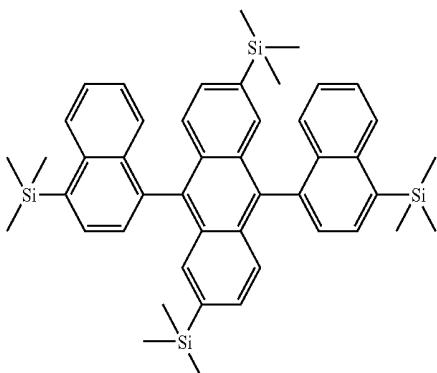


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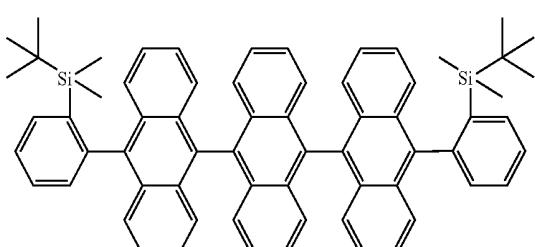
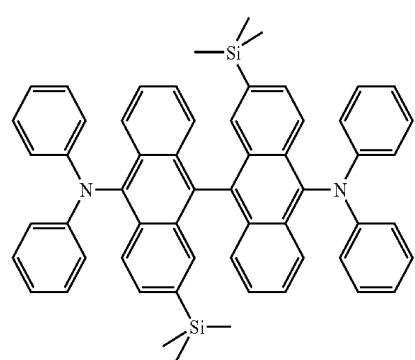
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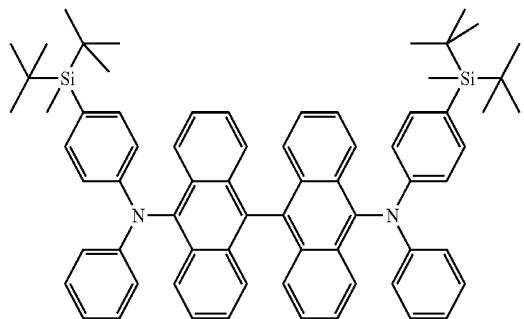


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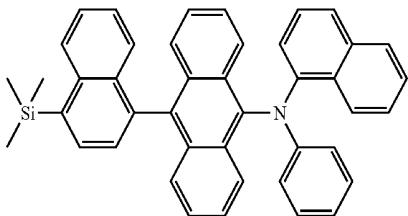
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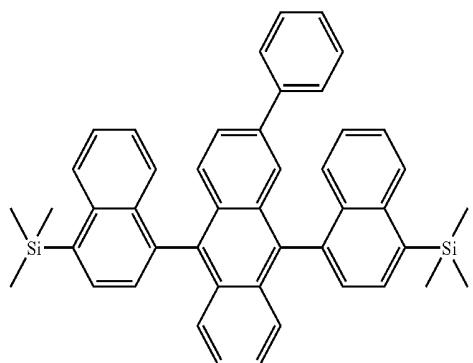
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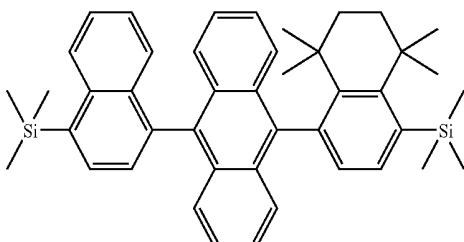


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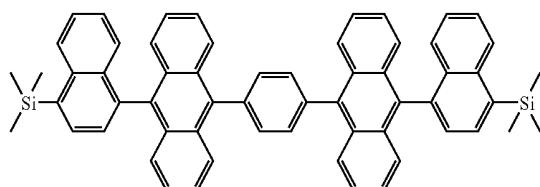
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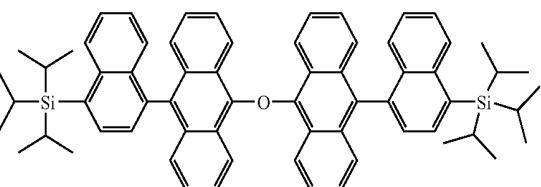
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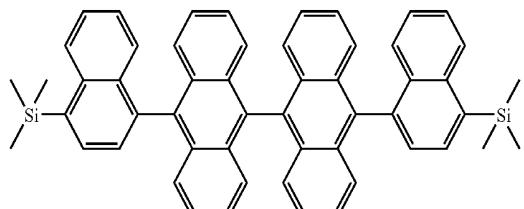
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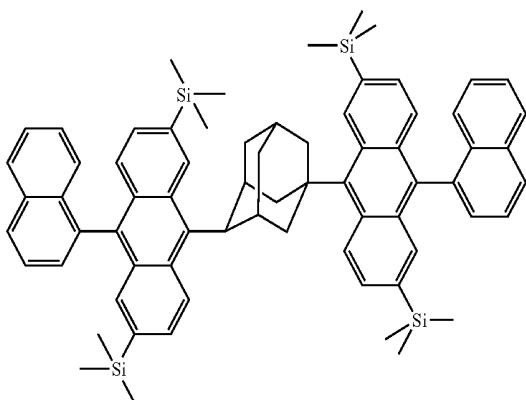
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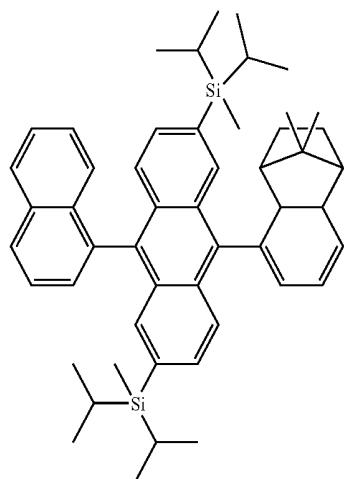


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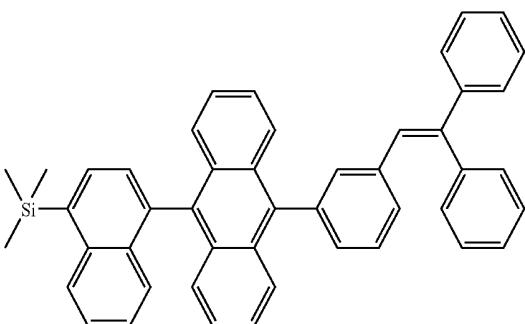


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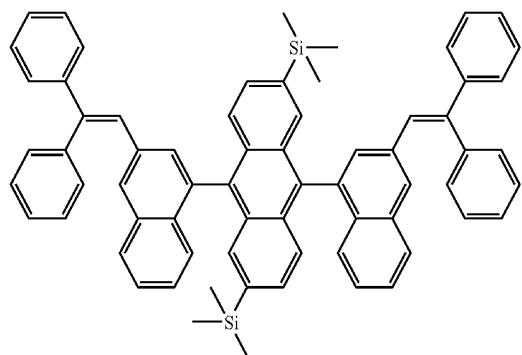
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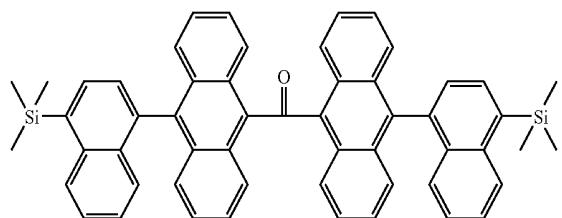
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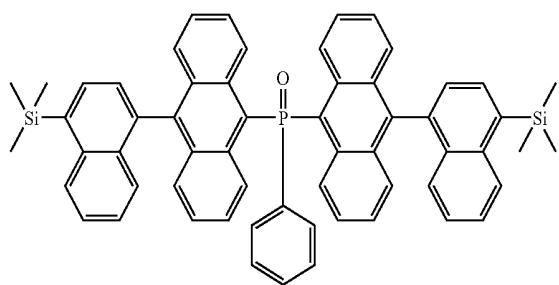
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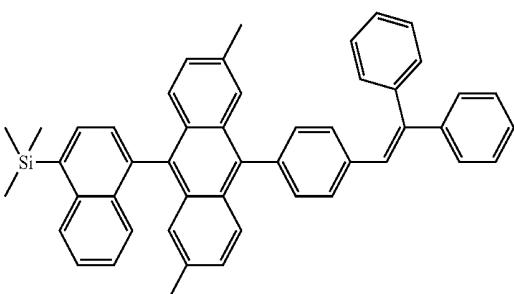
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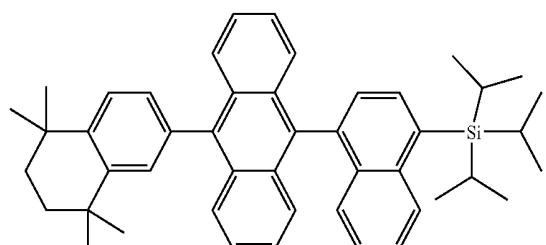
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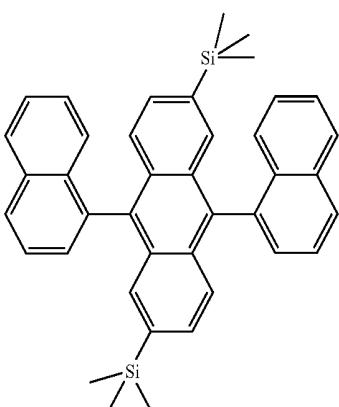
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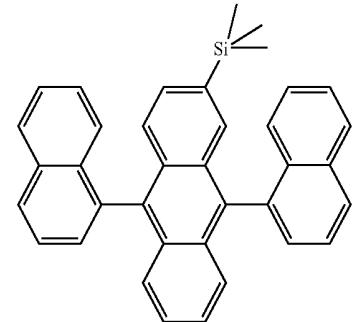
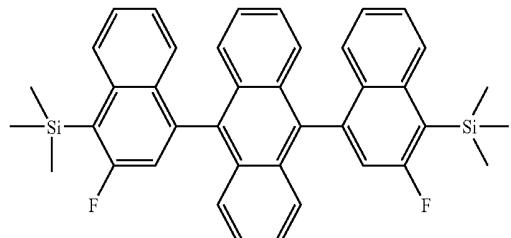


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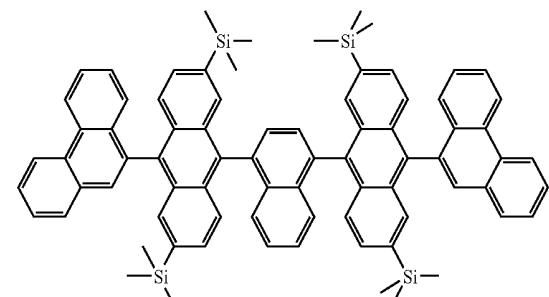
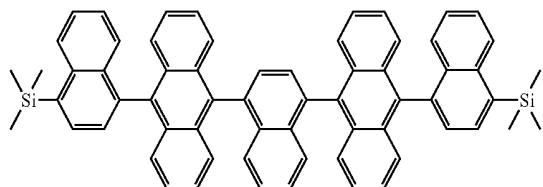
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(A28)



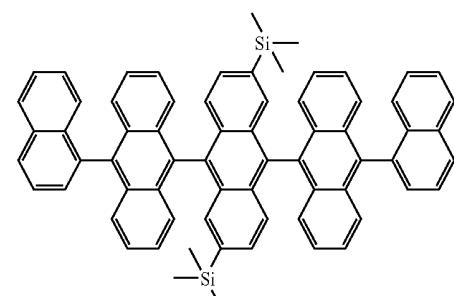
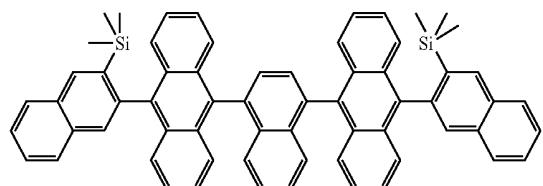
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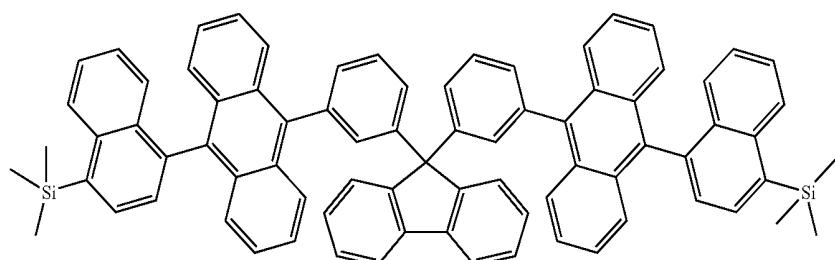


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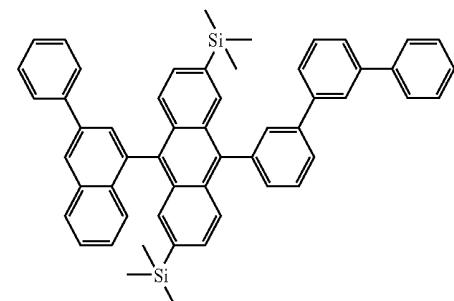
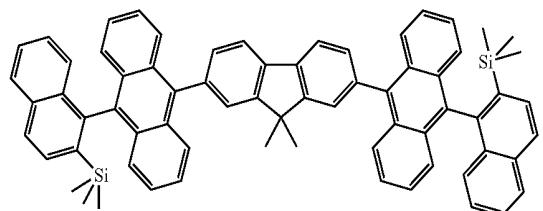


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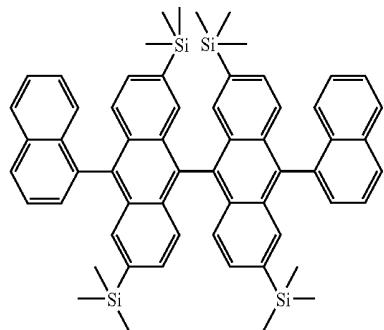


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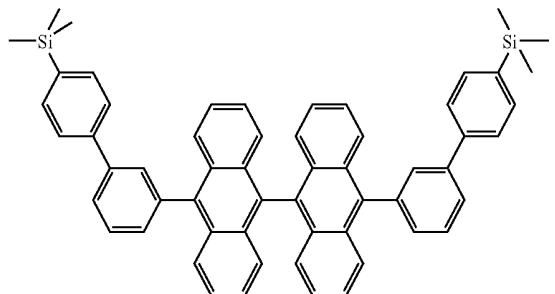


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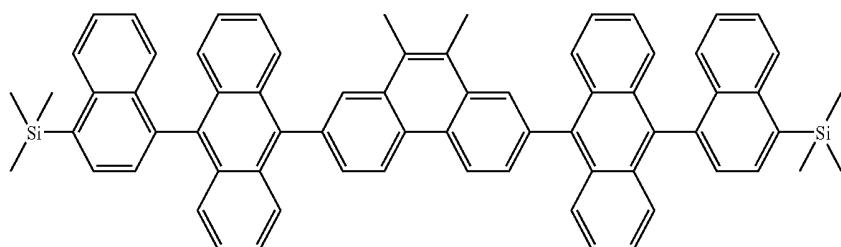
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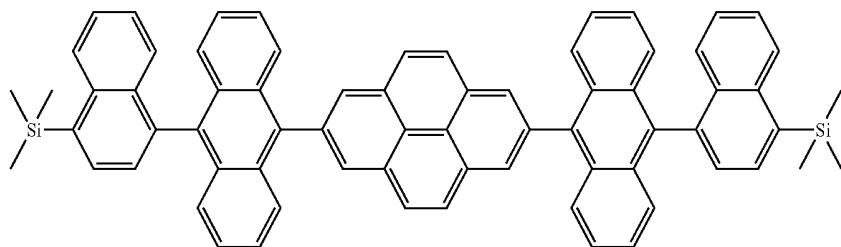


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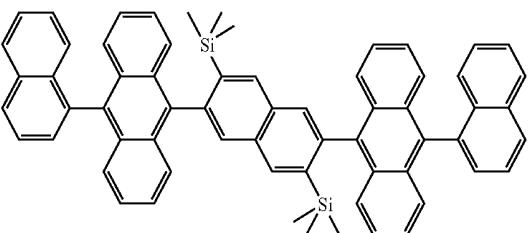
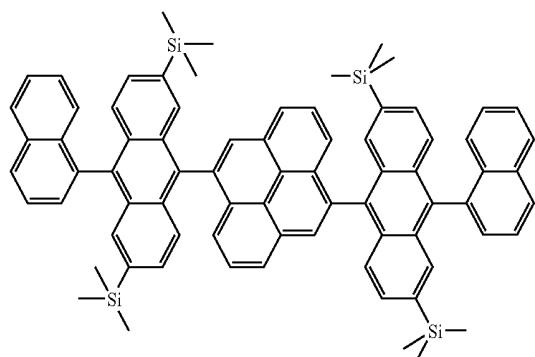


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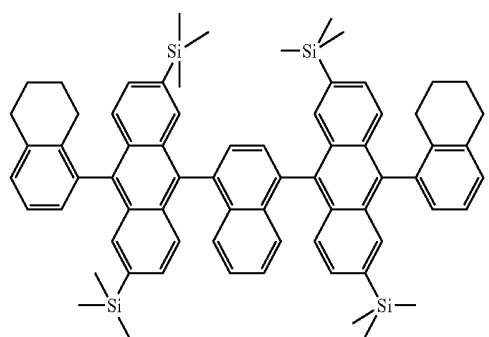


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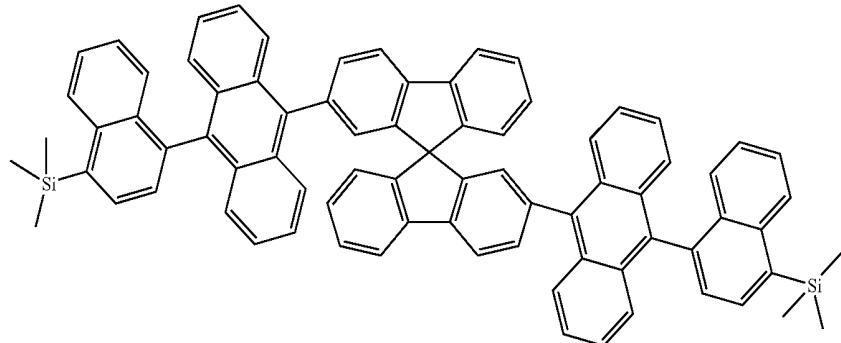


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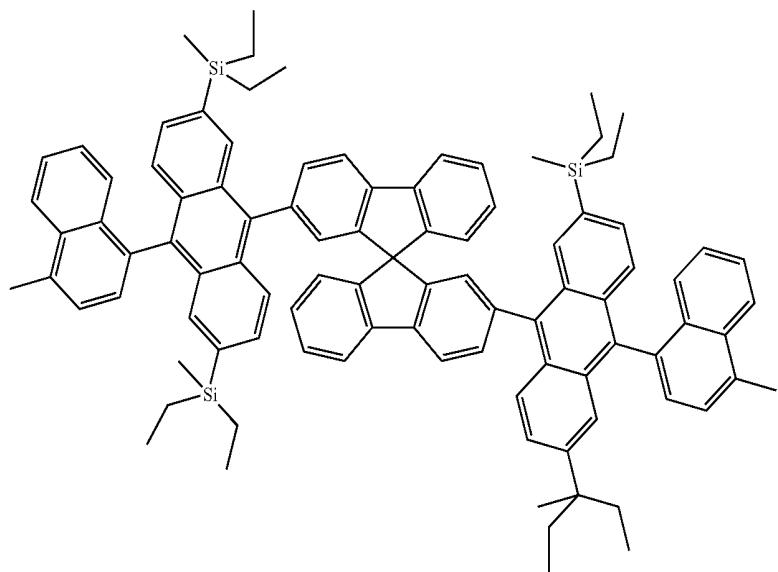


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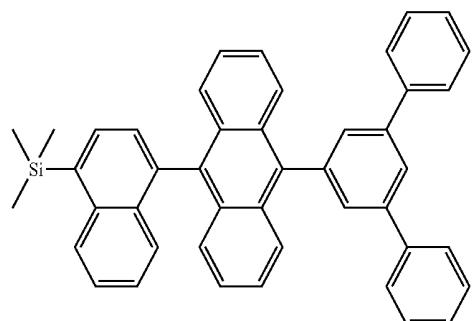
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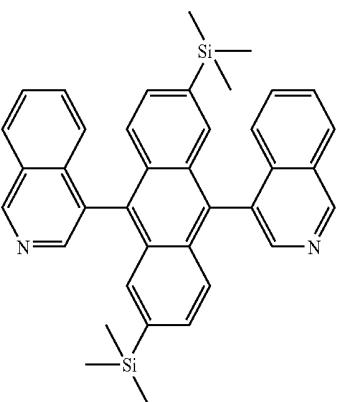
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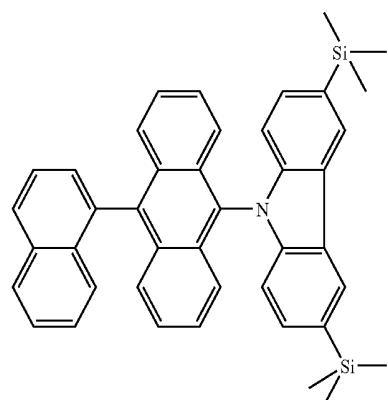


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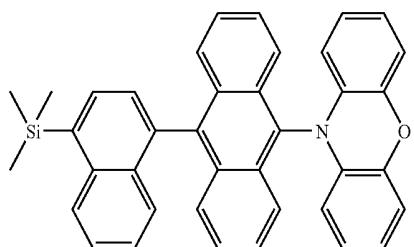


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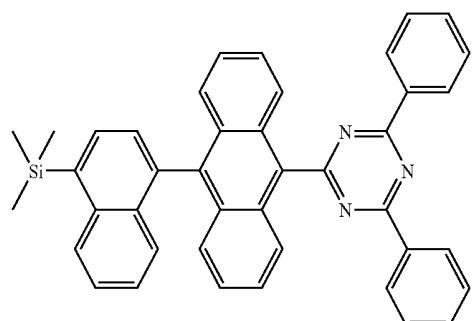


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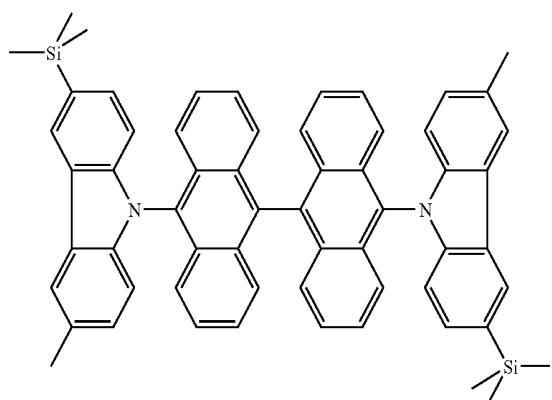
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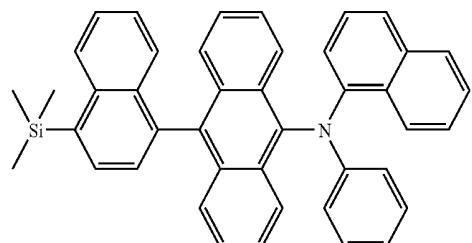
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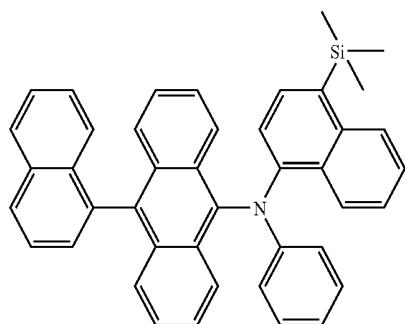
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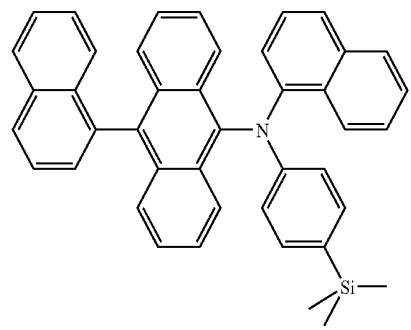
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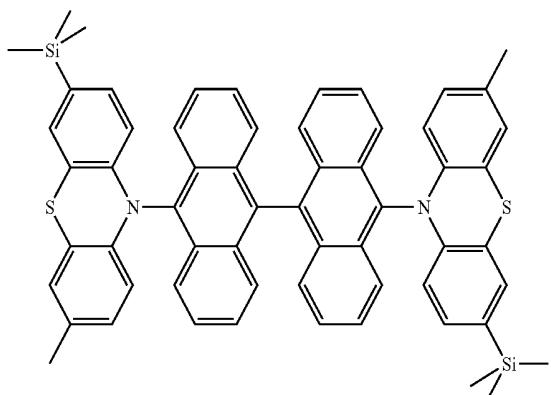
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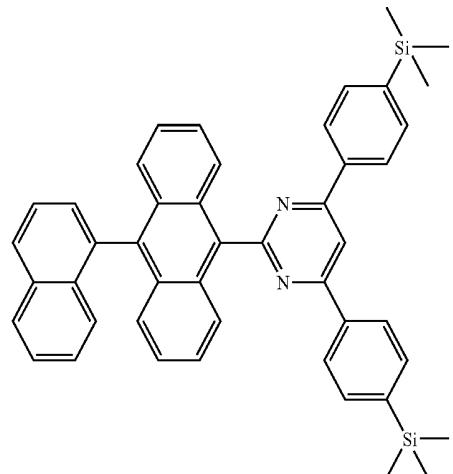
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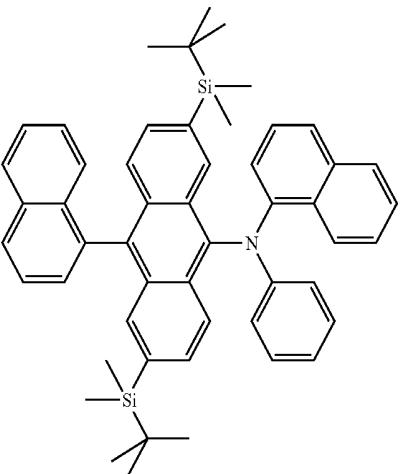
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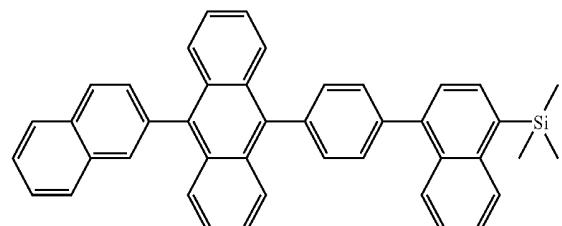
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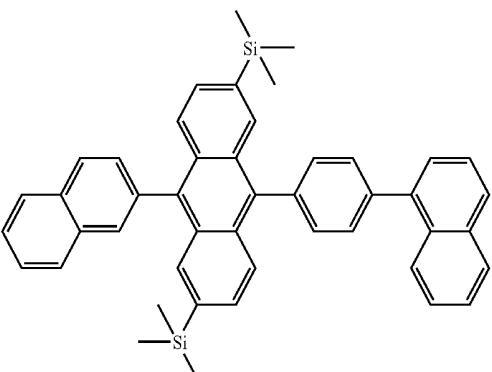
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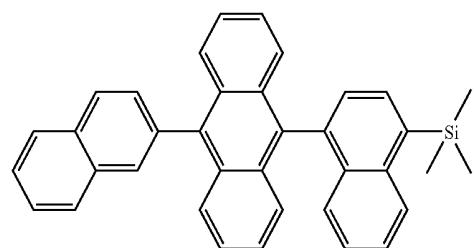
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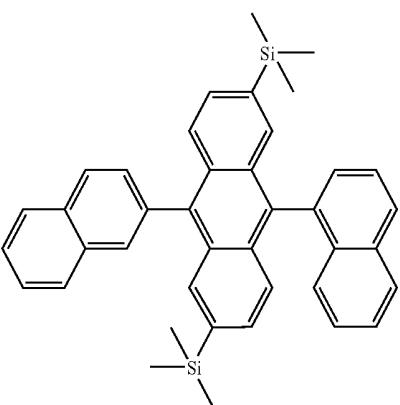
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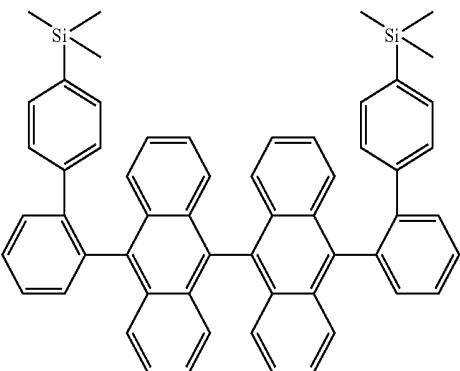
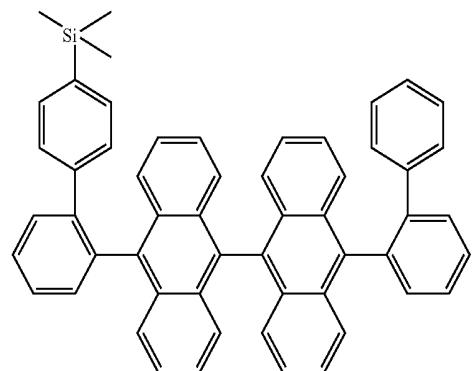
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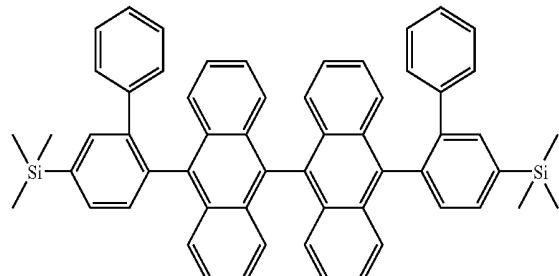


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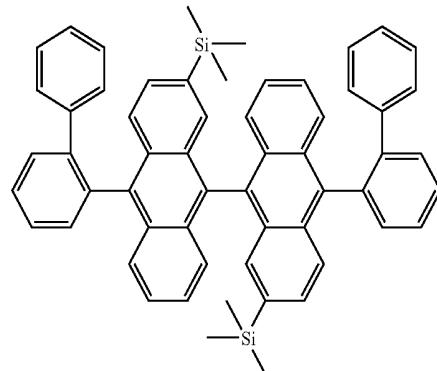


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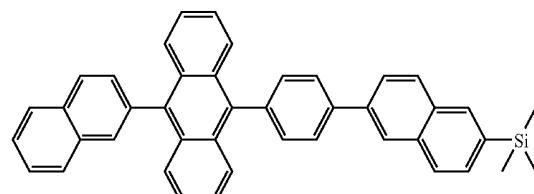




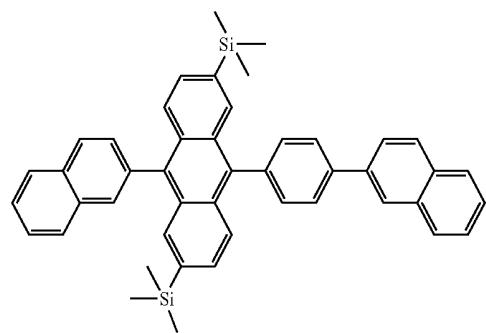
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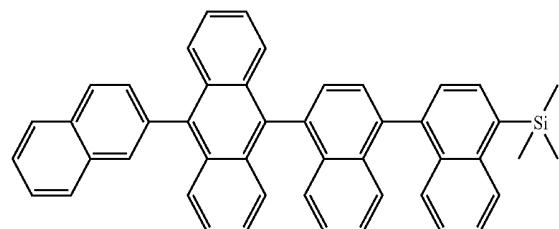
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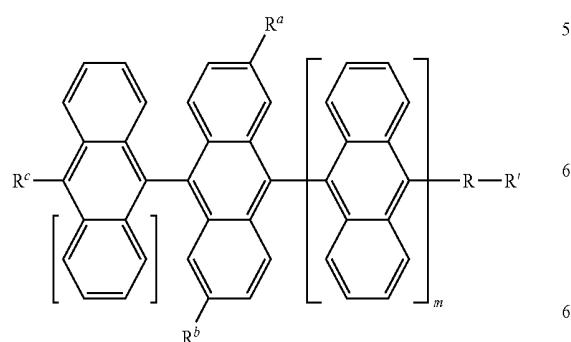
(A68)



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Table 1 below indicates further preferred structures of the formula (1). Preference is likewise given here to the structures which, instead of groups of the formula $\text{Si}(\text{Me})_3$, contain groups of the formula $\text{SiMe}_2(\text{t-Bu})$, $\text{SiMe}(\text{t-Bu})_2$ or $\text{Si}(\text{i-Pr})_3$. The symbols and indices used in the table relate to the formula (3) depicted below:

Formel (3)



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No.	R	Preferred structures of the formula (3)					
		Ra	Rb	Rc	d	m	R'
1	Phenyl	H	H	$\text{Si}(\text{Me})_3$	0	0	H
2	Phenyl	H	H	$\text{Si}(\text{Me})_3$	0	1	H
3	Phenyl	H	H	$\text{Si}(\text{Me})_3$	1	0	H
4	Phenyl	H	H	$\text{Si}(\text{Me})_3$	1	1	H
5	Phenyl	H	$\text{Si}(\text{Me})_3$	H	0	0	H
6	Phenyl	H	$\text{Si}(\text{Me})_3$	H	0	1	H
7	Phenyl	H	$\text{Si}(\text{Me})_3$	H	1	0	H
8	Phenyl	H	$\text{Si}(\text{Me})_3$	H	1	1	H
9	Phenyl	H	$\text{Si}(\text{Me})_3$	$\text{Si}(\text{Me})_3$	0	0	H
10	Phenyl	H	$\text{Si}(\text{Me})_3$	$\text{Si}(\text{Me})_3$	0	1	H
11	Phenyl	H	$\text{Si}(\text{Me})_3$	$\text{Si}(\text{Me})_3$	1	0	H
12	Phenyl	H	$\text{Si}(\text{Me})_3$	$\text{Si}(\text{Me})_3$	1	1	H

d=0 here means that the corresponding group is a 1-naphthyl group. Furthermore the abbreviation $\text{N}(\text{Ph})_2$ in Table 1 stands for a diphenylamino group, $\text{N}(\text{p-Tol})_2$ stands for a bis(para-tolyl)amino group and $\text{N}(\text{Ph})(1\text{-Naph})$ stands for a N-phenyl-N-(1-naphthyl)amino group.

TABLE 1-continued

Preferred structures of the formula (3)							
No.	R	Ra	Rb	Rc	d	m	R'
13	Phenyl	H	Si(Me)3	Methyl	0	0	H
14	Phenyl	H	Si(Me)3	Methyl	0	1	H
15	Phenyl	H	Si(Me)3	Methyl	1	0	H
16	Phenyl	H	Si(Me)3	Methyl	1	1	H
17	Phenyl	H	Si(Me)3	F	0	0	H
18	Phenyl	H	Si(Me)3	F	0	1	H
19	Phenyl	H	Si(Me)3	F	1	0	H
20	Phenyl	H	Si(Me)3	F	1	1	H
21	Phenyl	H	Si(Me)3	Phenyl	0	0	H
22	Phenyl	H	Si(Me)3	Phenyl	0	1	H
23	Phenyl	H	Si(Me)3	Phenyl	1	0	H
24	Phenyl	H	Si(Me)3	Phenyl	1	1	H
25	Phenyl	Si(Me)3	H	H	0	0	H
26	Phenyl	Si(Me)3	H	H	0	1	H
27	Phenyl	Si(Me)3	H	H	1	0	H
28	Phenyl	Si(Me)3	H	H	1	1	H
29	Phenyl	Si(Me)3	H	Si(Me)3	0	0	H
30	Phenyl	Si(Me)3	H	Si(Me)3	0	1	H
31	Phenyl	Si(Me)3	H	Si(Me)3	1	0	H
32	Phenyl	Si(Me)3	H	Si(Me)3	1	1	H
33	Phenyl	Si(Me)3	H	Methyl	0	0	H
34	Phenyl	Si(Me)3	H	Methyl	0	1	H
35	Phenyl	Si(Me)3	H	Methyl	1	0	H
36	Phenyl	Si(Me)3	H	Methyl	1	1	H
37	Phenyl	Si(Me)3	H	F	0	0	H
38	Phenyl	Si(Me)3	H	F	0	1	H
39	Phenyl	Si(Me)3	H	F	1	0	H
40	Phenyl	Si(Me)3	H	F	1	1	H
41	Phenyl	Si(Me)3	H	Phenyl	0	0	H
42	Phenyl	Si(Me)3	H	Phenyl	0	1	H
43	Phenyl	Si(Me)3	H	Phenyl	1	0	H
44	Phenyl	Si(Me)3	H	Phenyl	1	1	H
45	Phenyl	Si(Me)3	Si(Me)3	H	0	0	H
46	Phenyl	Si(Me)3	Si(Me)3	H	0	1	H
47	Phenyl	Si(Me)3	Si(Me)3	H	1	0	H
48	Phenyl	Si(Me)3	Si(Me)3	H	1	1	H
49	Phenyl	Si(Me)3	Si(Me)3	Si(Me)3	0	0	H
50	Phenyl	Si(Me)3	Si(Me)3	Si(Me)3	0	1	H
51	Phenyl	Si(Me)3	Si(Me)3	Si(Me)3	1	0	H
52	Phenyl	Si(Me)3	Si(Me)3	Si(Me)3	1	1	H
53	Phenyl	Si(Me)3	Si(Me)3	Methyl	0	0	H
54	Phenyl	Si(Me)3	Si(Me)3	Methyl	0	1	H
55	Phenyl	Si(Me)3	Si(Me)3	Methyl	1	0	H
56	Phenyl	Si(Me)3	Si(Me)3	Methyl	1	1	H
57	Phenyl	Si(Me)3	Si(Me)3	F	0	0	H
58	Phenyl	Si(Me)3	Si(Me)3	F	0	1	H
59	Phenyl	Si(Me)3	Si(Me)3	F	1	0	H
60	Phenyl	Si(Me)3	Si(Me)3	F	1	1	H
61	Phenyl	Si(Me)3	Si(Me)3	Phenyl	0	0	H
62	Phenyl	Si(Me)3	Si(Me)3	Phenyl	0	1	H
63	Phenyl	Si(Me)3	Si(Me)3	Phenyl	1	0	H
64	Phenyl	Si(Me)3	Si(Me)3	Phenyl	1	1	H
65	Phenyl	H	H	H	0	0	Si(Me)3
66	Phenyl	H	H	H	0	1	Si(Me)3
67	Phenyl	H	H	H	1	0	Si(Me)3
68	Phenyl	H	H	H	1	1	Si(Me)3
69	Phenyl	H	H	Si(Me)3	0	0	Si(Me)3
70	Phenyl	H	H	Si(Me)3	0	1	Si(Me)3
71	Phenyl	H	H	Si(Me)3	1	0	Si(Me)3
72	Phenyl	H	H	Si(Me)3	1	1	Si(Me)3
73	Phenyl	H	H	Methyl	0	0	Si(Me)3
74	Phenyl	H	H	Methyl	0	1	Si(Me)3
75	Phenyl	H	H	Methyl	1	0	Si(Me)3
76	Phenyl	H	H	Methyl	1	1	Si(Me)3
77	Phenyl	H	H	F	0	0	Si(Me)3
78	Phenyl	H	H	F	0	1	Si(Me)3
79	Phenyl	H	H	F	1	0	Si(Me)3
80	Phenyl	H	H	F	1	1	Si(Me)3
81	Phenyl	H	H	Phenyl	0	0	Si(Me)3
82	Phenyl	H	H	Phenyl	0	1	Si(Me)3
83	Phenyl	H	H	Phenyl	1	0	Si(Me)3
84	Phenyl	H	H	Phenyl	1	1	Si(Me)3
85	Phenyl	H	Si(Me)3	H	0	0	Si(Me)3
86	Phenyl	H	Si(Me)3	H	0	1	Si(Me)3
87	Phenyl	H	Si(Me)3	H	1	0	Si(Me)3
88	Phenyl	H	Si(Me)3	H	1	1	Si(Me)3

TABLE 1-continued

Preferred structures of the formula (3)							
No.	R	Ra	Rb	Rc	d	m	R'
89	Phenyl	H	Si(Me)3	Si(Me)3	0	0	Si(Me)3
90	Phenyl	H	Si(Me)3	Si(Me)3	0	1	Si(Me)3
91	Phenyl	H	Si(Me)3	Si(Me)3	1	0	Si(Me)3
92	Phenyl	H	Si(Me)3	Si(Me)3	1	1	Si(Me)3
93	Phenyl	H	Si(Me)3	Methyl	0	0	Si(Me)3
94	Phenyl	H	Si(Me)3	Methyl	0	1	Si(Me)3
95	Phenyl	H	Si(Me)3	Methyl	1	0	Si(Me)3
96	Phenyl	H	Si(Me)3	Methyl	1	1	Si(Me)3
97	Phenyl	H	Si(Me)3	F	0	0	Si(Me)3
98	Phenyl	H	Si(Me)3	F	0	1	Si(Me)3
99	Phenyl	H	Si(Me)3	F	1	0	Si(Me)3
100	Phenyl	H	Si(Me)3	F	1	1	Si(Me)3
101	Phenyl	H	Si(Me)3	Phenyl	0	0	Si(Me)3
102	Phenyl	H	Si(Me)3	Phenyl	0	1	Si(Me)3
103	Phenyl	H	Si(Me)3	Phenyl	1	0	Si(Me)3
104	Phenyl	H	Si(Me)3	Phenyl	1	1	Si(Me)3
105	Phenyl	Si(Me)3	H	H	0	0	Si(Me)3
106	Phenyl	Si(Me)3	H	H	0	1	Si(Me)3
107	Phenyl	Si(Me)3	H	H	1	0	Si(Me)3
108	Phenyl	Si(Me)3	H	H	1	1	Si(Me)3
109	Phenyl	Si(Me)3	H	Si(Me)3	0	0	Si(Me)3
110	Phenyl	Si(Me)3	H	Si(Me)3	0	1	Si(Me)3
111	Phenyl	Si(Me)3	H	Si(Me)3	1	0	Si(Me)3
112	Phenyl	Si(Me)3	H	Si(Me)3	1	1	Si(Me)3
113	Phenyl	Si(Me)3	H	Methyl	0	0	Si(Me)3
114	Phenyl	Si(Me)3	H	Methyl	0	1	Si(Me)3
115	Phenyl	Si(Me)3	H	Methyl	1	0	Si(Me)3
116	Phenyl	Si(Me)3	H	Methyl	1	1	Si(Me)3
117	Phenyl	Si(Me)3	H	F	0	0	Si(Me)3
118	Phenyl	Si(Me)3	H	F	0	1	Si(Me)3
119	Phenyl	Si(Me)3	H	F	1	0	Si(Me)3
120	Phenyl	Si(Me)3	H	F	1	1	Si(Me)3
121	Phenyl	Si(Me)3	H	Phenyl	0	0	Si(Me)3
122	Phenyl	Si(Me)3	H	Phenyl	0	1	Si(Me)3
123	Phenyl	Si(Me)3	H	Phenyl	1	0	Si(Me)3
124	Phenyl	Si(Me)3	H	Phenyl	1	1	Si(Me)3
125	Phenyl	Si(Me)3	Si(Me)3	H	0	0	Si(Me)3
126	Phenyl	Si(Me)3	Si(Me)3	H	0	1	Si(Me)3
127	Phenyl	Si(Me)3	Si(Me)3	H	1	0	Si(Me)3
128	Phenyl	Si(Me)3	Si(Me)3	H	1	1	Si(Me)3
129	Phenyl	Si(Me)3	Si(Me)3	Si(Me)3	0	0	Si(Me)3
130	Phenyl	Si(Me)3	Si(Me)3	Si(Me)3	0	1	Si(Me)3
131	Phenyl	Si(Me)3	Si(Me)3	Si(Me)3	1	0	Si(Me)3
132	Phenyl	Si(Me)3	Si(Me)3	Si(Me)3	1	1	Si(Me)3
133	Phenyl	Si(Me)3	Si(Me)3	Methyl	0	0	Si(Me)3
134	Phenyl	Si(Me)3	Si(Me)3	Methyl	0	1	Si(Me)3
135	Phenyl	Si(Me)3	Si(Me)3	Methyl	1	0	Si(Me)3
136	Phenyl	Si(Me)3	Si(Me)3	Methyl	1	1	Si(Me)3
137	Phenyl	Si(Me)3	Si(Me)3	F	0	0	Si(Me)3
138	Phenyl	Si(Me)3	Si(Me)3	F	0	1	Si(Me)3
139	Phenyl	Si(Me)3	Si(Me)3	F	1	0	Si(Me)3
140	Phenyl	Si(Me)3	Si(Me)3	F	1	1	Si(Me)3
141	Phenyl	Si(Me)3	Si(Me)3	Phenyl	0	0	Si(Me)3
142	Phenyl	Si(Me)3	Si(Me)3	Phenyl	0	1	Si(Me)3
143	Phenyl	Si(Me)3	Si(Me)3	Phenyl	1	0	Si(Me)3
144	Phenyl	Si(Me)3	Si(Me)3	Phenyl	1	1	Si(Me)3
145	1-Naphthyl	H	H	Si(Me)3	0	0	H
146	1-Naphthyl	H	H	Si(Me)3	0	1	H
147	1-Naphthyl	H	H	Si(Me)3	1	0	H
148	1-Naphthyl	H	H	Si(Me)3	1	1	H
149	1-Naphthyl	H	H	Si(Me)3	0	0	H
150	1-Naphthyl	H	H	Si(Me)3	0	1	H
151	1-Naphthyl	H	H	Si(Me)3	1	0	H
152	1-Naphthyl	H	H	Si(Me)3	1	1	H
153	1-Naphthyl	H	H	Si(Me)3	0	0	H
154	1-Naphthyl	H	H	Si(Me)3	0	1	H
155	1-Naphthyl	H	H	Si(Me)3	1	0	H
156	1-Naphthyl	H	H	Si(Me)3	1	1	H
157	1-Naphthyl	H	H	Methyl	0	0	H
158	1-Naphthyl	H	H	Methyl	0	1	H
159	1-Naphthyl	H	H	Methyl	1	0	H
160	1-Naphthyl	H	H	Methyl	1	1	H
161	1-Naphthyl	H	H	F	0	0	H
162	1-Naphthyl	H	H	F	0	1	H
163	1-Naphthyl	H	H	F	1	0	H
164	1-Naphthyl	H	H	F	1	1	H

TABLE 1-continued

Preferred structures of the formula (3)							
No.	R	Ra	Rb	Rc	d	m	R'
165	1-Naphthyl	H	Si(Me)3	Phenyl	0	0	H
166	1-Naphthyl	H	Si(Me)3	Phenyl	0	1	H
167	1-Naphthyl	H	Si(Me)3	Phenyl	1	0	H
168	1-Naphthyl	H	Si(Me)3	Phenyl	1	1	H
169	1-Naphthyl	Si(Me)3	H	H	0	0	H
170	1-Naphthyl	Si(Me)3	H	H	0	1	H
171	1-Naphthyl	Si(Me)3	H	H	1	0	H
172	1-Naphthyl	Si(Me)3	H	H	1	1	H
173	1-Naphthyl	Si(Me)3	H	Si(Me)3	0	0	H
174	1-Naphthyl	Si(Me)3	H	Si(Me)3	0	1	H
175	1-Naphthyl	Si(Me)3	H	Si(Me)3	1	0	H
176	1-Naphthyl	Si(Me)3	H	Si(Me)3	1	1	H
177	1-Naphthyl	Si(Me)3	H	Methyl	0	0	H
178	1-Naphthyl	Si(Me)3	H	Methyl	0	1	H
179	1-Naphthyl	Si(Me)3	H	Methyl	1	0	H
180	1-Naphthyl	Si(Me)3	H	Methyl	1	1	H
181	1-Naphthyl	Si(Me)3	H	F	0	0	H
182	1-Naphthyl	i(Me)3	H	F	0	1	H
183	1-Naphthyl	Si(Me)3	H	F	1	0	H
184	1-Naphthyl	Si(Me)3	H	F	1	1	H
185	1-Naphthyl	Si(Me)3	H	Phenyl	0	0	H
186	1-Naphthyl	Si(Me)3	H	Phenyl	0	1	H
187	1-Naphthyl	Si(Me)3	H	Phenyl	1	0	H
188	1-Naphthyl	Si(Me)3	H	Phenyl	1	1	H
189	1-Naphthyl	Si(Me)3	Si(Me)3	H	0	0	H
190	1-Naphthyl	Si(Me)3	Si(Me)3	H	0	1	H
191	1-Naphthyl	Si(Me)3	Si(Me)3	H	1	0	H
192	1-Naphthyl	Si(Me)3	Si(Me)3	H	1	1	H
193	1-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	0	0	H
194	1-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	0	1	H
195	1-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	1	0	H
196	1-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	1	1	H
197	1-Naphthyl	Si(Me)3	Si(Me)3	Methyl	0	0	H
198	1-Naphthyl	Si(Me)3	Si(Me)3	Methyl	0	1	H
199	1-Naphthyl	Si(Me)3	Si(Me)3	Methyl	1	0	H
200	1-Naphthyl	Si(Me)3	Si(Me)3	Methyl	1	1	H
201	1-Naphthyl	Si(Me)3	Si(Me)3	F	0	0	H
202	1-Naphthyl	Si(Me)3	Si(Me)3	F	0	1	H
203	1-Naphthyl	Si(Me)3	Si(Me)3	F	1	0	H
204	1-Naphthyl	Si(Me)3	Si(Me)3	F	1	1	H
205	1-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	0	0	H
206	1-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	0	1	H
207	1-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	1	0	H
208	1-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	1	1	H
209	1-Naphthyl	H	H	H	0	0	Si(Me)3
210	1-Naphthyl	H	H	H	0	1	Si(Me)3
211	1-Naphthyl	H	H	H	1	0	Si(Me)3
212	1-Naphthyl	H	H	H	1	1	Si(Me)3
213	1-Naphthyl	H	H	Si(Me)3	0	0	Si(Me)3
214	1-Naphthyl	H	H	Si(Me)3	0	1	Si(Me)3
215	1-Naphthyl	H	H	Si(Me)3	1	0	Si(Me)3
216	1-Naphthyl	H	H	Si(Me)3	1	1	Si(Me)3
217	1-Naphthyl	H	H	Methyl	0	0	Si(Me)3
218	1-Naphthyl	H	H	Methyl	0	1	Si(Me)3
219	1-Naphthyl	H	H	Methyl	1	0	Si(Me)3
220	1-Naphthyl	H	H	Methyl	1	1	Si(Me)3
221	1-Naphthyl	H	H	F	0	0	Si(Me)3
222	1-Naphthyl	H	H	F	0	1	Si(Me)3
223	1-Naphthyl	H	H	F	1	0	Si(Me)3
224	1-Naphthyl	H	H	F	1	1	Si(Me)3
225	1-Naphthyl	H	H	Phenyl	0	0	Si(Me)3
226	1-Naphthyl	H	H	Phenyl	0	1	Si(Me)3
227	1-Naphthyl	H	H	Phenyl	1	0	Si(Me)3
228	1-Naphthyl	H	H	Phenyl	1	1	Si(Me)3
229	1-Naphthyl	H	Si(Me)3	H	0	0	Si(Me)3
230	1-Naphthyl	H	Si(Me)3	H	0	1	Si(Me)3
231	1-Naphthyl	H	Si(Me)3	H	1	0	Si(Me)3
232	1-Naphthyl	H	Si(Me)3	H	1	1	Si(Me)3
233	1-Naphthyl	H	Si(Me)3	Si(Me)3	0	0	Si(Me)3
234	1-Naphthyl	H	Si(Me)3	Si(Me)3	0	1	Si(Me)3
235	1-Naphthyl	H	Si(Me)3	Si(Me)3	1	0	Si(Me)3
236	1-Naphthyl	H	Si(Me)3	Si(Me)3	1	1	Si(Me)3
237	1-Naphthyl	H	Si(Me)3	Methyl	0	0	Si(Me)3
238	1-Naphthyl	H	Si(Me)3	Methyl	0	1	Si(Me)3
239	1-Naphthyl	H	Si(Me)3	Methyl	1	0	Si(Me)3
240	1-Naphthyl	H	Si(Me)3	Methyl	1	1	Si(Me)3

TABLE 1-continued

Preferred structures of the formula (3)								
No.	R	Ra	Rb	Rc	d	m	R'	
241	1-Naphthyl	H	Si(Me)3	F	0	0	Si(Me)3	
242	1-Naphthyl	H	Si(Me)3	F	0	1	Si(Me)3	
243	1-Naphthyl	H	Si(Me)3	F	1	0	Si(Me)3	
244	1-Naphthyl	H	Si(Me)3	F	1	1	Si(Me)3	
245	1-Naphthyl	H	Si(Me)3	Phenyl	0	0	Si(Me)3	
246	1-Naphthyl	H	Si(Me)3	Phenyl	0	1	Si(Me)3	
247	1-Naphthyl	H	Si(Me)3	Phenyl	1	0	Si(Me)3	
248	1-Naphthyl	H	Si(Me)3	Phenyl	1	1	Si(Me)3	
249	1-Naphthyl	Si(Me)3	H	H	0	0	Si(Me)3	
250	1-Naphthyl	Si(Me)3	H	H	0	1	Si(Me)3	
251	1-Naphthyl	Si(Me)3	H	H	1	0	Si(Me)3	
252	1-Naphthyl	Si(Me)3	H	H	1	1	Si(Me)3	
253	1-Naphthyl	Si(Me)3	H	Si(Me)3	0	0	Si(Me)3	
254	1-Naphthyl	Si(Me)3	H	Si(Me)3	0	1	Si(Me)3	
255	1-Naphthyl	Si(Me)3	H	Si(Me)3	1	0	Si(Me)3	
256	1-Naphthyl	Si(Me)3	H	Si(Me)3	1	1	Si(Me)3	
257	1-Naphthyl	Si(Me)3	H	Methyl	0	0	Si(Me)3	
258	1-Naphthyl	Si(Me)3	H	Methyl	0	1	Si(Me)3	
259	1-Naphthyl	Si(Me)3	H	Methyl	1	0	Si(Me)3	
260	1-Naphthyl	Si(Me)3	H	Methyl	1	1	Si(Me)3	
261	1-Naphthyl	Si(Me)3	H	F	0	0	Si(Me)3	
262	1-Naphthyl	Si(Me)3	H	F	0	1	Si(Me)3	
263	1-Naphthyl	Si(Me)3	H	F	1	0	Si(Me)3	
264	1-Naphthyl	Si(Me)3	H	F	1	1	Si(Me)3	
265	1-Naphthyl	Si(Me)3	H	Phenyl	0	0	Si(Me)3	
266	1-Naphthyl	Si(Me)3	H	Phenyl	0	1	Si(Me)3	
267	1-Naphthyl	Si(Me)3	H	Phenyl	1	0	Si(Me)3	
268	1-Naphthyl	Si(Me)3	H	Phenyl	1	1	Si(Me)3	
269	1-Naphthyl	Si(Me)3	Si(Me)3	H	0	0	Si(Me)3	
270	1-Naphthyl	Si(Me)3	Si(Me)3	H	0	1	Si(Me)3	
271	1-Naphthyl	Si(Me)3	Si(Me)3	H	1	0	Si(Me)3	
272	1-Naphthyl	Si(Me)3	Si(Me)3	H	1	1	Si(Me)3	
273	1-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	0	0	Si(Me)3	
274	1-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	0	1	Si(Me)3	
275	1-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	1	0	Si(Me)3	
276	1-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	1	1	Si(Me)3	
277	1-Naphthyl	Si(Me)3	Si(Me)3	Methyl	0	0	Si(Me)3	
278	1-Naphthyl	Si(Me)3	Si(Me)3	Methyl	0	1	Si(Me)3	
279	1-Naphthyl	Si(Me)3	Si(Me)3	Methyl	1	0	Si(Me)3	
280	1-Naphthyl	Si(Me)3	Si(Me)3	Methyl	1	1	Si(Me)3	
281	1-Naphthyl	Si(Me)3	Si(Me)3	F	0	0	Si(Me)3	
282	1-Naphthyl	Si(Me)3	Si(Me)3	F	0	1	Si(Me)3	
283	1-Naphthyl	Si(Me)3	Si(Me)3	F	1	0	Si(Me)3	
284	1-Naphthyl	Si(Me)3	Si(Me)3	F	1	1	Si(Me)3	
285	1-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	0	0	Si(Me)3	
286	1-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	0	1	Si(Me)3	
287	1-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	1	0	Si(Me)3	
288	1-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	1	1	Si(Me)3	
289	2-Naphthyl	H	H	Si(Me)3	0	0	H	
290	2-Naphthyl	H	H	Si(Me)3	0	1	H	
291	2-Naphthyl	H	H	Si(Me)3	1	0	H	
292	2-Naphthyl	H	H	Si(Me)3	1	1	H	
293	2-Naphthyl	H	H	Si(Me)3	0	0	H	
294	2-Naphthyl	H	H	Si(Me)3	0	1	H	
295	2-Naphthyl	H	H	Si(Me)3	1	0	H	
296	2-Naphthyl	H	H	Si(Me)3	1	1	H	
297	2-Naphthyl	H	H	Si(Me)3	0	0	H	
298	2-Naphthyl	H	H	Si(Me)3	0	1	H	
299	2-Naphthyl	H	H	Si(Me)3	1	0	H	
300	2-Naphthyl	H	H	Si(Me)3	1	1	H	
301	2-Naphthyl	H	H	Si(Me)3	Methyl	0	H	
302	2-Naphthyl	H	H	Si(Me)3	Methyl	0	1	H
303	2-Naphthyl	H	H	Si(Me)3	Methyl	1	0	H
304	2-Naphthyl	H	H	Si(Me)3	Methyl	1	1	H
305	2-Naphthyl	H	H	Si(Me)3	F	0	H	
306	2-Naphthyl	H	H	Si(Me)3	F	0	1	H
307	2-Naphthyl	H	H	Si(Me)3	F	1	0	H
308	2-Naphthyl	H	H	Si(Me)3	F	1	1	H
309	2-Naphthyl	H	H	Si(Me)3	Phenyl	0	H	
310	2-Naphthyl	H	H	Si(Me)3	Phenyl	0	1	H
311	2-Naphthyl	H	H	Si(Me)3	Phenyl	1	0	H
312	2-Naphthyl	H	H	Si(Me)3	Phenyl	1	1	H
313	2-Naphthyl	H	H	Si(Me)3	H	0	H	
314	2-Naphthyl	H	H	Si(Me)3	H	0	H	
315	2-Naphthyl	H	H	Si(Me)3	H	1	0	H
316	2-Naphthyl	H	H	Si(Me)3	H	1	1	H

TABLE 1-continued

Preferred structures of the formula (3)							
No.	R	Ra	Rb	Rc	d	m	R'
317	2-Naphthyl	Si(Me)3	H	Si(Me)3	0	0	H
318	2-Naphthyl	Si(Me)3	H	Si(Me)3	0	1	H
319	2-Naphthyl	Si(Me)3	H	Si(Me)3	1	0	H
320	2-Naphthyl	Si(Me)3	H	Si(Me)3	1	1	H
321	2-Naphthyl	Si(Me)3	H	Methyl	0	0	H
322	2-Naphthyl	Si(Me)3	H	Methyl	0	1	H
323	2-Naphthyl	Si(Me)3	H	Methyl	1	0	H
324	2-Naphthyl	Si(Me)3	H	Methyl	1	1	H
325	2-Naphthyl	Si(Me)3	H	F	0	0	H
326	2-Naphthyl	Si(Me)3	H	F	0	1	H
327	2-Naphthyl	Si(Me)3	H	F	1	0	H
328	2-Naphthyl	Si(Me)3	H	F	1	1	H
329	2-Naphthyl	Si(Me)3	H	Phenyl	0	0	H
330	2-Naphthyl	Si(Me)3	H	Phenyl	0	1	H
331	2-Naphthyl	Si(Me)3	H	Phenyl	1	0	H
332	2-Naphthyl	Si(Me)3	H	Phenyl	1	1	H
333	2-Naphthyl	Si(Me)3	Si(Me)3	H	0	0	H
334	2-Naphthyl	Si(Me)3	Si(Me)3	H	0	1	H
335	2-Naphthyl	Si(Me)3	Si(Me)3	H	1	0	H
336	2-Naphthyl	Si(Me)3	Si(Me)3	H	1	1	H
337	2-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	0	0	H
338	2-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	0	1	H
339	2-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	1	0	H
340	2-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	1	1	H
341	2-Naphthyl	Si(Me)3	Si(Me)3	Methyl	0	0	H
342	2-Naphthyl	Si(Me)3	Si(Me)3	Methyl	0	1	H
343	2-Naphthyl	Si(Me)3	Si(Me)3	Methyl	1	0	H
344	2-Naphthyl	Si(Me)3	Si(Me)3	Methyl	1	1	H
345	2-Naphthyl	Si(Me)3	Si(Me)3	F	0	0	H
346	2-Naphthyl	Si(Me)3	Si(Me)3	F	0	1	H
347	2-Naphthyl	Si(Me)3	Si(Me)3	F	1	0	H
348	2-Naphthyl	Si(Me)3	Si(Me)3	F	1	1	H
349	2-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	0	0	H
350	2-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	0	1	H
351	2-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	1	0	H
352	2-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	1	1	H
353	2-Naphthyl	H	H	H	0	0	Si(Me)3
354	2-Naphthyl	H	H	H	0	1	Si(Me)3
355	2-Naphthyl	H	H	H	1	0	Si(Me)3
356	2-Naphthyl	H	H	H	1	1	Si(Me)3
357	2-Naphthyl	H	H	Si(Me)3	0	0	Si(Me)3
358	2-Naphthyl	H	H	Si(Me)3	0	1	Si(Me)3
359	2-Naphthyl	H	H	Si(Me)3	1	0	Si(Me)3
360	2-Naphthyl	H	H	Si(Me)3	1	1	Si(Me)3
361	2-Naphthyl	H	H	Methyl	0	0	Si(Me)3
362	2-Naphthyl	H	H	Methyl	0	1	Si(Me)3
363	2-Naphthyl	H	H	Methyl	1	0	Si(Me)3
364	2-Naphthyl	H	H	Methyl	1	1	Si(Me)3
365	2-Naphthyl	H	H	F	0	0	Si(Me)3
366	2-Naphthyl	H	H	F	0	1	Si(Me)3
367	2-Naphthyl	H	H	F	1	0	Si(Me)3
368	2-Naphthyl	H	H	F	1	1	Si(Me)3
369	2-Naphthyl	H	H	Phenyl	0	0	Si(Me)3
370	2-Naphthyl	H	H	Phenyl	0	1	Si(Me)3
371	2-Naphthyl	H	H	Phenyl	1	0	Si(Me)3
372	2-Naphthyl	H	H	Phenyl	1	1	Si(Me)3
373	2-Naphthyl	H	Si(Me)3	H	0	0	Si(Me)3
374	2-Naphthyl	H	Si(Me)3	H	0	1	Si(Me)3
375	2-Naphthyl	H	Si(Me)3	H	1	0	Si(Me)3
376	2-Naphthyl	H	Si(Me)3	H	1	1	Si(Me)3
377	2-Naphthyl	H	Si(Me)3	Si(Me)3	0	0	Si(Me)3
378	2-Naphthyl	H	Si(Me)3	Si(Me)3	0	1	Si(Me)3
379	2-Naphthyl	H	Si(Me)3	Si(Me)3	1	0	Si(Me)3
380	2-Naphthyl	H	Si(Me)3	Si(Me)3	1	1	Si(Me)3
381	2-Naphthyl	H	Si(Me)3	Methyl	0	0	Si(Me)3
382	2-Naphthyl	H	Si(Me)3	Methyl	0	1	Si(Me)3
383	2-Naphthyl	H	Si(Me)3	Methyl	1	0	Si(Me)3
384	2-Naphthyl	H	Si(Me)3	Methyl	1	1	Si(Me)3
385	2-Naphthyl	H	Si(Me)3	F	0	0	Si(Me)3
386	2-Naphthyl	H	Si(Me)3	F	0	1	Si(Me)3
387	2-Naphthyl	H	Si(Me)3	F	1	0	Si(Me)3
388	2-Naphthyl	H	Si(Me)3	F	1	1	Si(Me)3
389	2-Naphthyl	H	Si(Me)3	Phenyl	0	0	Si(Me)3
390	2-Naphthyl	H	Si(Me)3	Phenyl	0	1	Si(Me)3
391	2-Naphthyl	H	Si(Me)3	Phenyl	1	0	Si(Me)3
392	2-Naphthyl	H	Si(Me)3	Phenyl	1	1	Si(Me)3

TABLE 1-continued

Preferred structures of the formula (3)							
No.	R	Ra	Rb	Rc	d	m	R'
393	2-Naphthyl	Si(Me)3	H	H	0	0	Si(Me)3
394	2-Naphthyl	Si(Me)3	H	H	0	1	Si(Me)3
395	2-Naphthyl	Si(Me)3	H	H	1	0	Si(Me)3
396	2-Naphthyl	Si(Me)3	H	H	1	1	Si(Me)3
397	2-Naphthyl	Si(Me)3	H	Si(Me)3	0	0	Si(Me)3
398	2-Naphthyl	Si(Me)3	H	Si(Me)3	0	1	Si(Me)3
399	2-Naphthyl	Si(Me)3	H	Si(Me)3	1	0	Si(Me)3
400	2-Naphthyl	Si(Me)3	H	Si(Me)3	1	1	Si(Me)3
401	2-Naphthyl	Si(Me)3	H	Methyl	0	0	Si(Me)3
402	2-Naphthyl	Si(Me)3	H	Methyl	0	1	Si(Me)3
403	2-Naphthyl	Si(Me)3	H	Methyl	1	0	Si(Me)3
404	2-Naphthyl	Si(Me)3	H	Methyl	1	1	Si(Me)3
405	2-Naphthyl	Si(Me)3	H	F	0	0	Si(Me)3
406	2-Naphthyl	Si(Me)3	H	F	0	1	Si(Me)3
407	2-Naphthyl	Si(Me)3	H	F	1	0	Si(Me)3
408	2-Naphthyl	Si(Me)3	H	F	1	1	Si(Me)3
409	2-Naphthyl	Si(Me)3	H	Phenyl	0	0	Si(Me)3
410	2-Naphthyl	Si(Me)3	H	Phenyl	0	1	Si(Me)3
411	2-Naphthyl	Si(Me)3	H	Phenyl	1	0	Si(Me)3
412	2-Naphthyl	Si(Me)3	H	Phenyl	1	1	Si(Me)3
413	2-Naphthyl	Si(Me)3	Si(Me)3	H	0	0	Si(Me)3
414	2-Naphthyl	Si(Me)3	Si(Me)3	H	0	1	Si(Me)3
415	2-Naphthyl	Si(Me)3	Si(Me)3	H	1	0	Si(Me)3
416	2-Naphthyl	Si(Me)3	Si(Me)3	H	1	1	Si(Me)3
417	2-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	0	0	Si(Me)3
418	2-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	0	1	Si(Me)3
419	2-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	1	0	Si(Me)3
420	2-Naphthyl	Si(Me)3	Si(Me)3	Si(Me)3	1	1	Si(Me)3
421	2-Naphthyl	Si(Me)3	Si(Me)3	Methyl	0	0	Si(Me)3
422	2-Naphthyl	Si(Me)3	Si(Me)3	Methyl	0	1	Si(Me)3
423	2-Naphthyl	Si(Me)3	Si(Me)3	Methyl	1	0	Si(Me)3
424	2-Naphthyl	Si(Me)3	Si(Me)3	Methyl	1	1	Si(Me)3
425	2-Naphthyl	Si(Me)3	Si(Me)3	F	0	0	Si(Me)3
426	2-Naphthyl	Si(Me)3	Si(Me)3	F	0	1	Si(Me)3
427	2-Naphthyl	Si(Me)3	Si(Me)3	F	1	0	Si(Me)3
428	2-Naphthyl	Si(Me)3	Si(Me)3	F	1	1	Si(Me)3
429	-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	0	0	Si(Me)3
430	2-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	0	1	Si(Me)3
431	2-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	1	0	Si(Me)3
432	2-Naphthyl	Si(Me)3	Si(Me)3	Phenyl	1	1	Si(Me)3
433	para-Tolyl	H	H	Si(Me)3	0	0	—
434	para-Tolyl	H	H	Si(Me)3	0	1	—
435	para-Tolyl	H	H	Si(Me)3	1	0	—
436	para-Tolyl	H	H	Si(Me)3	1	1	—
437	para-Tolyl	H	H	Si(Me)3	0	0	—
438	para-Tolyl	H	H	Si(Me)3	0	1	—
439	para-Tolyl	H	H	Si(Me)3	1	0	—
440	para-Tolyl	H	H	Si(Me)3	1	1	—
441	para-Tolyl	H	H	Si(Me)3	0	0	—
442	para-Tolyl	H	H	Si(Me)3	0	1	—
443	para-Tolyl	H	H	Si(Me)3	1	0	—
444	para-Tolyl	H	H	Si(Me)3	1	1	—
445	para-Tolyl	H	H	Si(Me)3	Methyl	0	—
446	para-Tolyl	H	H	Si(Me)3	Methyl	0	1
447	para-Tolyl	H	H	Si(Me)3	Methyl	1	0
448	para-Tolyl	H	H	Si(Me)3	Methyl	1	1
449	para-Tolyl	H	H	Si(Me)3	F	0	—
450	para-Tolyl	H	H	Si(Me)3	F	0	1
451	para-Tolyl	H	H	Si(Me)3	F	1	0
452	para-Tolyl	H	H	Si(Me)3	F	1	1
453	para-Tolyl	H	H	Si(Me)3	Phenyl	0	—
454	para-Tolyl	H	H	Si(Me)3	Phenyl	0	1
455	para-Tolyl	H	H	Si(Me)3	Phenyl	1	0
456	para-Tolyl	H	H	Si(Me)3	Phenyl	1	1
457	para-Tolyl	Si(Me)3	H	H	0	0	—
458	para-Tolyl	Si(Me)3	H	H	0	1	—
459	para-Tolyl	Si(Me)3	H	H	1	0	—
460	para-Tolyl	Si(Me)3	H	H	1	1	—
461	para-Tolyl	Si(Me)3	H	Si(Me)3	0	0	—
462	para-Tolyl	Si(Me)3	H	Si(Me)3	0	1	—
463	para-Tolyl	Si(Me)3	H	Si(Me)3	1	0	—
464	para-Tolyl	Si(Me)3	H	Si(Me)3	1	1	—
465	para-Tolyl	Si(Me)3	H	Si(Me)3	Methyl	0	—
466	para-Tolyl	Si(Me)3	H	Si(Me)3	Methyl	0	1
467	para-Tolyl	Si(Me)3	H	Si(Me)3	Methyl	1	0
468	para-Tolyl	Si(Me)3	H	Si(Me)3	Methyl	1	1

TABLE 1-continued

Preferred structures of the formula (3)							
No.	R	Ra	Rb	Rc	d	m	R'
469	para-Tolyl	Si(Me)3	H	F	0	0	—
470	para-Tolyl	Si(Me)3	H	F	0	1	—
471	para-Tolyl	Si(Me)3	H	F	1	0	—
472	para-Tolyl	Si(Me)3	H	F	1	1	—
473	para-Tolyl	Si(Me)3	H	Phenyl	0	0	—
474	para-Tolyl	Si(Me)3	H	Phenyl	0	1	—
475	para-Tolyl	Si(Me)3	H	Phenyl	1	0	—
476	para-Tolyl	Si(Me)3	H	Phenyl	1	1	—
477	para-Tolyl	Si(Me)3	Si(Me)3	H	0	0	—
478	para-Tolyl	Si(Me)3	Si(Me)3	H	0	1	—
479	para-Tolyl	Si(Me)3	Si(Me)3	H	1	0	—
480	para-Tolyl	Si(Me)3	Si(Me)3	H	1	1	—
481	para-Tolyl	Si(Me)3	Si(Me)3	Si(Me)3	0	0	—
482	para-Tolyl	Si(Me)3	Si(Me)3	Si(Me)3	0	1	—
483	para-Tolyl	Si(Me)3	Si(Me)3	Si(Me)3	1	0	—
484	para-Tolyl	Si(Me)3	Si(Me)3	Si(Me)3	1	1	—
485	para-Tolyl	Si(Me)3	Si(Me)3	Methyl	0	0	—
486	para-Tolyl	Si(Me)3	Si(Me)3	Methyl	0	1	—
487	para-Tolyl	Si(Me)3	Si(Me)3	Methyl	1	0	—
488	para-Tolyl	Si(Me)3	Si(Me)3	Methyl	1	1	—
489	para-Tolyl	Si(Me)3	Si(Me)3	F	0	0	—
490	para-Tolyl	Si(Me)3	Si(Me)3	F	0	1	—
491	para-Tolyl	Si(Me)3	Si(Me)3	F	1	0	—
492	para-Tolyl	Si(Me)3	Si(Me)3	F	1	1	—
493	para-Tolyl	Si(Me)3	Si(Me)3	Phenyl	0	0	—
494	para-Tolyl	Si(Me)3	Si(Me)3	Phenyl	0	1	—
495	para-Tolyl	Si(Me)3	Si(Me)3	Phenyl	1	0	—
496	para-Tolyl	Si(Me)3	Si(Me)3	Phenyl	1	1	—
497	2-Biphenyl	H	H	Si(Me)3	0	0	—
498	2-Biphenyl	H	H	Si(Me)3	0	1	—
499	2-Biphenyl	H	H	Si(Me)3	1	0	—
500	2-Biphenyl	H	H	Si(Me)3	1	1	—
501	2-Biphenyl	H	Si(Me)3	H	0	0	—
502	2-Biphenyl	H	Si(Me)3	H	0	1	—
503	2-Biphenyl	H	Si(Me)3	H	1	0	—
504	2-Biphenyl	H	Si(Me)3	H	1	1	—
505	2-Biphenyl	H	Si(Me)3	Si(Me)3	0	0	—
506	2-Biphenyl	H	Si(Me)3	Si(Me)3	0	1	—
507	2-Biphenyl	H	Si(Me)3	Si(Me)3	1	0	—
508	2-Biphenyl	H	Si(Me)3	Si(Me)3	1	1	—
509	2-Biphenyl	H	Si(Me)3	Methyl	0	0	—
510	2-Biphenyl	H	Si(Me)3	Methyl	0	1	—
511	2-phenyl	H	Si(Me)3	Methyl	1	0	—
512	2-Biphenyl	H	Si(Me)3	Methyl	1	1	—
513	2-Biphenyl	H	Si(Me)3	F	0	0	—
514	2-Biphenyl	H	Si(Me)3	F	0	1	—
515	2-Biphenyl	H	Si(Me)3	F	1	0	—
516	2-Biphenyl	H	Si(Me)3	F	1	1	—
517	2-Biphenyl	H	Si(Me)3	Phenyl	0	0	—
518	2-Biphenyl	H	Si(Me)3	Phenyl	0	1	—
519	2-Biphenyl	H	Si(Me)3	Phenyl	1	0	—
520	2-Biphenyl	H	Si(Me)3	Phenyl	1	1	—
521	2-Biphenyl	Si(Me)3	H	H	0	0	—
522	2-Biphenyl	Si(Me)3	H	H	0	1	—
523	2-Biphenyl	Si(Me)3	H	H	1	0	—
524	2-Biphenyl	Si(Me)3	H	H	1	1	—
525	2-Biphenyl	Si(Me)3	H	Si(Me)3	0	0	—
526	2-Biphenyl	Si(Me)3	H	Si(Me)3	0	1	—
527	2-Biphenyl	Si(Me)3	H	Si(Me)3	1	0	—
528	2-Biphenyl	Si(Me)3	H	Si(Me)3	1	1	—
529	2-Biphenyl	Si(Me)3	H	Methyl	0	0	—
530	2-Biphenyl	Si(Me)3	H	Methyl	0	1	—
531	2-Biphenyl	Si(Me)3	H	Methyl	1	0	—
532	2-Biphenyl	Si(Me)3	H	Methyl	1	1	—
533	2-Biphenyl	Si(Me)3	H	F	0	0	—
534	2-Biphenyl	Si(Me)3	H	F	0	1	—
535	2-Biphenyl	Si(Me)3	H	F	1	0	—
536	2-Biphenyl	Si(Me)3	H	F	1	1	—
537	2-Biphenyl	Si(Me)3	H	Phenyl	0	0	—
538	2-Biphenyl	Si(Me)3	H	Phenyl	0	1	—
539	2-Biphenyl	Si(Me)3	H	Phenyl	1	0	—
540	2-Biphenyl	Si(Me)3	H	Phenyl	1	1	—
541	2-Biphenyl	Si(Me)3	Si(Me)3	H	0	0	—
542	2-Biphenyl	Si(Me)3	Si(Me)3	H	0	1	—
543	2-Biphenyl	Si(Me)3	Si(Me)3	H	1	0	—
544	2-Biphenyl	Si(Me)3	Si(Me)3	H	1	1	—

TABLE 1-continued

Preferred structures of the formula (3)							
No.	R	Ra	Rb	Rc	d	m	R'
545	2-Biphenyl	Si(Me)3	Si(Me)3	Si(Me)3	0	0	—
546	2-Biphenyl	Si(Me)3	Si(Me)3	Si(Me)3	0	1	—
547	2-Biphenyl	Si(Me)3	Si(Me)3	Si(Me)3	1	0	—
548	2-Biphenyl	Si(Me)3	Si(Me)3	Si(Me)3	1	1	—
549	2-Biphenyl	Si(Me)3	Si(Me)3	Methyl	0	0	—
550	2-Biphenyl	Si(Me)3	Si(Me)3	Methyl	0	1	—
551	2-Biphenyl	Si(Me)3	Si(Me)3	Methyl	1	0	—
552	2-Biphenyl	Si(Me)3	Si(Me)3	Methyl	1	1	—
553	2-Biphenyl	Si(Me)3	Si(Me)3	F	0	0	—
554	2-Biphenyl	Si(Me)3	Si(Me)3	F	0	1	—
555	2-Biphenyl	Si(Me)3	Si(Me)3	F	1	0	—
556	2-Biphenyl	Si(Me)3	Si(Me)3	F	1	1	—
557	2-Biphenyl	Si(Me)3	Si(Me)3	Phenyl	0	0	—
558	2-Biphenyl	Si(Me)3	Si(Me)3	Phenyl	0	1	—
559	2-Biphenyl	Si(Me)3	Si(Me)3	Phenyl	1	0	—
560	2-Biphenyl	Si(Me)3	Si(Me)3	Phenyl	1	1	—
561	N(Ph)2	H	H	Si(Me)3	0	0	—
562	N(Ph)2	H	H	Si(Me)3	0	1	—
563	N(Ph)2	H	H	Si(Me)3	1	0	—
564	N(Ph)2	H	H	Si(Me)3	1	1	—
565	N(Ph)2	H	Si(Me)3	H	0	0	—
566	N(Ph)2	H	Si(Me)3	H	0	1	—
567	N(Ph)2	H	Si(Me)3	H	1	0	—
568	N(Ph)2	H	Si(Me)3	H	1	1	—
569	N(Ph)2	H	Si(Me)3	Si(Me)3	0	0	—
570	N(Ph)2	H	Si(Me)3	Si(Me)3	0	1	—
571	N(Ph)2	H	Si(Me)3	Si(Me)3	1	0	—
572	N(Ph)2	H	Si(Me)3	Si(Me)3	1	1	—
573	N(Ph)2	H	Si(Me)3	Methyl	0	0	—
574	N(Ph)2	H	Si(Me)3	Methyl	0	1	—
575	N(Ph)2	H	Si(Me)3	Methyl	1	0	—
576	N(Ph)2	H	Si(Me)3	Methyl	1	1	—
577	N(Ph)2	H	Si(Me)3	F	0	0	—
578	N(Ph)2	H	Si(Me)3	F	0	1	—
579	N(Ph)2	H	Si(Me)3	F	1	0	—
580	N(Ph)2	H	Si(Me)3	F	1	1	—
581	N(Ph)2	H	Si(Me)3	Phenyl	0	0	—
582	N(Ph)2	H	Si(Me)3	Phenyl	0	1	—
583	N(Ph)2	H	Si(Me)3	Phenyl	1	0	—
584	N(Ph)2	H	Si(Me)3	Phenyl	1	1	—
585	N(Ph)2	H	Si(Me)3	H	0	0	—
586	N(Ph)2	H	Si(Me)3	H	0	1	—
587	N(Ph)2	H	Si(Me)3	H	1	0	—
588	N(Ph)2	H	Si(Me)3	H	1	1	—
589	N(Ph)2	H	Si(Me)3	Si(Me)3	0	0	—
590	N(Ph)2	H	Si(Me)3	Si(Me)3	0	1	—
591	N(Ph)2	H	Si(Me)3	Si(Me)3	1	0	—
592	N(Ph)2	H	Si(Me)3	Si(Me)3	1	1	—
593	N(Ph)2	H	Si(Me)3	Methyl	0	0	—
594	N(Ph)2	H	Si(Me)3	Methyl	0	1	—
595	N(Ph)2	H	Si(Me)3	Methyl	1	0	—
596	N(Ph)2	H	Si(Me)3	Methyl	1	1	—
597	N(Ph)2	H	Si(Me)3	F	0	0	—
598	N(Ph)2	H	Si(Me)3	F	0	1	—
599	N(Ph)2	H	Si(Me)3	F	1	0	—
600	N(Ph)2	H	Si(Me)3	F	1	1	—
601	N(Ph)2	H	Si(Me)3	Phenyl	0	0	—
602	N(Ph)2	H	Si(Me)3	Phenyl	0	1	—
603	N(Ph)2	H	Si(Me)3	Phenyl	1	0	—
604	N(Ph)2	H	Si(Me)3	Phenyl	1	1	—
605	N(Ph)2	H	Si(Me)3	Si(Me)3	0	0	—
606	N(Ph)2	H	Si(Me)3	Si(Me)3	0	1	—
607	N(Ph)2	H	Si(Me)3	Si(Me)3	1	0	—
608	N(Ph)2	H	Si(Me)3	Si(Me)3	1	1	—
609	N(Ph)2	H	Si(Me)3	Si(Me)3	0	0	—
610	N(Ph)2	H	Si(Me)3	Si(Me)3	0	1	—
611	N(Ph)2	H	Si(Me)3	Si(Me)3	1	0	—
612	N(Ph)2	H	Si(Me)3	Si(Me)3	1	1	—
613	N(Ph)2	H	Si(Me)3	Methyl	0	0	—
614	N(Ph)2	H	Si(Me)3	Methyl	0	1	—
615	N(Ph)2	H	Si(Me)3	Methyl	1	0	—
616	N(Ph)2	H	Si(Me)3	Methyl	1	1	—
617	N(Ph)2	H	Si(Me)3	F	0	0	—
618	N(Ph)2	H	Si(Me)3	F	0	1	—
619	N(Ph)2	H	Si(Me)3	F	1	0	—
620	N(Ph)2	H	Si(Me)3	F	1	1	—

TABLE 1-continued

Preferred structures of the formula (3)							
No.	R	Ra	Rb	Rc	d	m	R'
621	N(Ph)2	Si(Me)3	Si(Me)3	Phenyl	0	0	—
622	N(Ph)2	Si(Me)3	Si(Me)3	Phenyl	0	1	—
623	N(Ph)2	Si(Me)3	Si(Me)3	Phenyl	1	0	—
624	N(Ph)2	Si(Me)3	Si(Me)3	Phenyl	1	1	—
625	N(p-Tol)2	H	H	Si(Me)3	0	0	—
626	N(p-Tol)2	H	H	Si(Me)3	0	1	—
627	N(p-Tol)2	H	H	Si(Me)3	1	0	—
628	N(p-Tol)2	H	H	Si(Me)3	1	1	—
629	N(p-Tol)2	H	Si(Me)3	H	0	0	—
630	N(p-Tol)2	H	Si(Me)3	H	0	1	—
631	N(p-Tol)2	H	Si(Me)3	H	1	0	—
632	N(p-Tol)2	H	Si(Me)3	H	1	1	—
633	N(p-Tol)2	H	Si(Me)3	Si(Me)3	0	0	—
634	N(p-Tol)2	H	Si(Me)3	Si(Me)3	0	1	—
635	N(p-Tol)2	H	Si(Me)3	Si(Me)3	1	0	—
636	N(p-Tol)2	H	Si(Me)3	Si(Me)3	1	1	—
637	N(p-Tol)2	H	Si(Me)3	Methyl	0	0	—
638	N(p-Tol)2	H	Si(Me)3	Methyl	0	1	—
639	N(p-Tol)2	H	Si(Me)3	Methyl	1	0	—
640	N(p-Tol)2	H	Si(Me)3	Methyl	1	1	—
641	N(p-Tol)2	H	Si(Me)3	F	0	0	—
642	N(p-Tol)2	H	Si(Me)3	F	0	1	—
643	N(p-Tol)2	H	Si(Me)3	F	1	0	—
644	N(p-Tol)2	H	Si(Me)3	F	1	1	—
645	N(p-Tol)2	H	Si(Me)3	Phenyl	0	0	—
646	N(p-Tol)2	H	Si(Me)3	Phenyl	0	1	—
647	N(p-Tol)2	H	Si(Me)3	Phenyl	1	0	—
648	N(p-Tol)2	H	Si(Me)3	Phenyl	1	1	—
649	N(p-Tol)2	Si(Me)3	H	H	0	0	—
650	N(p-Tol)2	Si(Me)3	H	H	0	1	—
651	N(p-Tol)2	Si(Me)3	H	H	1	0	—
652	N(p-Tol)2	Si(Me)3	H	H	1	1	—
653	N(p-Tol)2	Si(Me)3	H	Si(Me)3	0	0	—
654	N(p-Tol)2	Si(Me)3	H	Si(Me)3	0	1	—
655	N(p-Tol)2	Si(Me)3	H	Si(Me)3	1	0	—
656	N(p-Tol)2	Si(Me)3	H	Si(Me)3	1	1	—
657	N(p-Tol)2	Si(Me)3	H	Methyl	0	0	—
658	N(p-Tol)2	Si(Me)3	H	Methyl	0	1	—
659	N(p-Tol)2	Si(Me)3	H	Methyl	1	0	—
660	N(p-Tol)2	Si(Me)3	H	Methyl	1	1	—
661	N(p-Tol)2	Si(Me)3	H	F	0	0	—
662	N(p-Tol)2	Si(Me)3	H	F	0	1	—
663	N(p-Tol)2	Si(Me)3	H	F	1	0	—
664	N(p-Tol)2	Si(Me)3	H	F	1	1	—
665	N(p-Tol)2	Si(Me)3	H	Phenyl	0	0	—
666	N(p-Tol)2	Si(Me)3	H	Phenyl	0	1	—
667	N(p-Tol)2	Si(Me)3	H	Phenyl	1	0	—
668	N(p-Tol)2	Si(Me)3	H	Phenyl	1	1	—
669	N(p-Tol)2	Si(Me)3	Si(Me)3	H	0	0	—
670	N(p-Tol)2	Si(Me)3	Si(Me)3	H	0	1	—
671	N(p-Tol)2	Si(Me)3	Si(Me)3	H	1	0	—
672	N(p-Tol)2	Si(Me)3	Si(Me)3	H	1	1	—
673	N(p-Tol)2	Si(Me)3	Si(Me)3	Si(Me)3	0	0	—
674	N(p-Tol)2	Si(Me)3	Si(Me)3	Si(Me)3	0	1	—
675	N(p-Tol)2	Si(Me)3	Si(Me)3	Si(Me)3	1	0	—
676	N(p-Tol)2	Si(Me)3	Si(Me)3	Si(Me)3	1	1	—
677	N(p-Tol)2	Si(Me)3	Si(Me)3	Methyl	0	0	—
678	N(p-Tol)2	Si(Me)3	Si(Me)3	Methyl	0	1	—
679	N(p-Tol)2	Si(Me)3	Si(Me)3	Methyl	1	0	—
680	N(p-Tol)2	Si(Me)3	Si(Me)3	Methyl	1	1	—
681	N(p-Tol)2	Si(Me)3	Si(Me)3	F	0	0	—
682	N(p-Tol)2	Si(Me)3	Si(Me)3	F	0	1	—
683	N(p-Tol)2	Si(Me)3	Si(Me)3	F	1	0	—
684	N(p-Tol)2	Si(Me)3	Si(Me)3	F	1	1	—
685	N(p-Tol)2	Si(Me)3	Si(Me)3	Phenyl	0	0	—
686	N(p-Tol)2	Si(Me)3	Si(Me)3	Phenyl	0	1	—
687	N(p-Tol)2	Si(Me)3	Si(Me)3	Phenyl	1	0	—
688	N(p-Tol)2	Si(Me)3	Si(Me)3	Phenyl	1	1	—
689	N(Ph)(1-Naph)	H	H	Si(Me)3	0	0	—
690	N(Ph)(1-Naph)	H	H	Si(Me)3	0	1	—
691	N(Ph)(1-Naph)	H	H	Si(Me)3	1	0	—
692	N(Ph)(1-Naph)	H	H	Si(Me)3	1	1	—
693	N(Ph)(1-Naph)	H	Si(Me)3	H	0	0	—
694	N(Ph)(1-Naph)	H	Si(Me)3	H	0	1	—
695	N(Ph)(1-Naph)	H	Si(Me)3	H	1	0	—
696	N(Ph)(1-Naph)	H	Si(Me)3	H	1	1	—

TABLE 1-continued

Preferred structures of the formula (3)							
No.	R	Ra	Rb	Rc	d	m	R'
697	N(Ph)(1-Naph)	H	Si(Me)3	Si(Me)3	0	0	—
698	N(Ph)(1-Naph)	H	Si(Me)3	Si(Me)3	0	1	—
699	N(Ph)(1-Naph)	H	Si(Me)3	Si(Me)3	1	0	—
700	N(Ph)(1-Naph)	H	Si(Me)3	Si(Me)3	1	1	—
701	N(Ph)(1-Naph)	H	Si(Me)3	Methyl	0	0	—
702	N(Ph)(1-Naph)	H	Si(Me)3	Methyl	0	1	—
703	N(Ph)(1-Naph)	H	Si(Me)3	Methyl	1	0	—
704	N(Ph)(1-Naph)	H	Si(Me)3	Methyl	1	1	—
705	N(Ph)(1-Naph)	H	Si(Me)3	F	0	0	—
706	N(Ph)(1-Naph)	H	Si(Me)3	F	0	1	—
707	N(Ph)(1-Naph)	H	Si(Me)3	F	1	0	—
708	N(Ph)(1-Naph)	H	Si(Me)3	F	1	1	—
709	N(Ph)(1-Naph)	H	Si(Me)3	Phenyl	0	0	—
710	N(Ph)(1-Naph)	H	Si(Me)3	Phenyl	0	1	—
711	N(Ph)(1-Naph)	H	Si(Me)3	Phenyl	1	0	—
712	N(Ph)(1-Naph)	H	Si(Me)3	Phenyl	1	1	—
713	N(Ph)(1-Naph)	Si(Me)3	H	H	0	0	—
714	N(Ph)(1-Naph)	Si(Me)3	H	H	0	1	—
715	N(Ph)(1-Naph)	Si(Me)3	H	H	1	0	—
716	N(Ph)(1-Naph)	Si(Me)3	H	H	1	1	—
717	N(Ph)(1-Naph)	Si(Me)3	H	Si(Me)3	0	0	—
718	N(Ph)(1-Naph)	Si(Me)3	H	Si(Me)3	0	1	—
719	N(Ph)(1-Naph)	Si(Me)3	H	Si(Me)3	1	0	—
720	N(Ph)(1-Naph)	Si(Me)3	H	Si(Me)3	1	1	—
721	N(Ph)(1-Naph)	Si(Me)3	H	Methyl	0	0	—
722	N(Ph)(1-Naph)	Si(Me)3	H	Methyl	0	1	—
723	N(Ph)(1-Naph)	Si(Me)3	H	Methyl	1	0	—
724	N(Ph)(1-Naph)	Si(Me)3	H	Methyl	1	1	—
725	N(Ph)(1-Naph)	Si(Me)3	H	F	0	0	—
726	N(Ph)(1-Naph)	Si(Me)3	H	F	0	1	—
727	N(Ph)(1-Naph)	Si(Me)3	H	F	1	0	—
728	N(Ph)(1-Naph)	Si(Me)3	H	F	1	1	—
729	N(Ph)(1-Naph)	Si(Me)3	H	Phenyl	0	0	—
730	N(Ph)(1-Naph)	Si(Me)3	H	Phenyl	0	1	—
731	N(Ph)(1-Naph)	Si(Me)3	H	Phenyl	1	0	—
732	N(Ph)(1-Naph)	Si(Me)3	H	Phenyl	1	1	—
733	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	H	0	0	—
734	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	H	0	1	—
735	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	H	1	0	—
736	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	H	1	1	—
737	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Si(Me)3	0	0	—
738	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Si(Me)3	0	1	—
739	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Si(Me)3	1	0	—
740	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Si(Me)3	1	1	—
741	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Methyl	0	0	—
742	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Methyl	0	1	—
743	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Methyl	1	0	—
744	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Methyl	1	1	—
745	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	F	0	0	—
746	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	F	0	1	—
747	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	F	1	0	—
748	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	F	1	1	—
749	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Phenyl	0	0	—
750	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Phenyl	0	1	—
751	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Phenyl	1	0	—
752	N(Ph)(1-Naph)	Si(Me)3	Si(Me)3	Phenyl	1	1	—

55 The compounds of the formula (1) can be employed in organic electroluminescent devices. Depending on the substitution pattern, they are suitable for use as host material, in particular for fluorescent emitters, as emitter, as hole-transport material, as hole-blocking material and/or as electron-transport material. The invention therefore furthermore relates to the use of compounds of the formula (1) in organic electronic devices, in particular in organic electroluminescent devices, in particular as host material, as emitter, as hole-transport material, as hole-blocking material and/or as electron-transport material.

60 The invention furthermore relates to organic electronic devices, in particular organic electroluminescent devices, comprising anode, cathode and at least one emitting layer,

where at least one layer comprises at least one compound of the formula (1). The layer comprising the compound of the formula (1) is preferably an emitting layer, a hole-transport layer, a hole-injection layer, a hole-blocking layer or an electron-transport layer.

Besides the cathode, anode and emitting layer (or emitting layers), the organic electroluminescent device may also comprise further layers. These can be, for example: hole-injection layer, hole-transport layer, hole-blocking layer, electron-transport layer, electron-injection layer and/or charge-generation layer (T. Matsumoto et al., *Multiphoton Organic EL Device Having Charge Generation Layer*, IDMC 2003, Taiwan; Session 21 OLED (5)). The materials in these layers may also be doped. Each of these layers does not necessarily have to be present. Suitable hole-transport materials are, for example, aromatic amines, as usually used in accordance with the prior art, which may also be p-doped. Suitable electron-transport materials are, for example, metal-chelate complexes, for example AlQ_3 , compounds based on electron-deficient heterocycles, for example triazine derivatives, or compounds containing aromatic carbonyls or phosphine oxides, as described, for example, in WO 05/084081 and WO 05/084082, each of which may also be n-doped. Suitable electron-injection materials are, in particular, fluorides and oxides of the alkali metals and alkaline earth metals, for example NaF , BaF_2 , CaF_2 , LiF or Li_2O .

If the symbol R stands for an aromatic or heteroaromatic ring system, in particular for a condensed aryl or heteroaryl group, the compound of the formula (1) is particularly suitable as host material, in particular for fluorescent emitters, and/or as electron-transport material and/or as hole-blocking material.

A host material is taken to mean the component in a system comprising host and dopant which is present in the greater proportion in the system. In a system comprising a host and a plurality of dopants, the host is taken to mean the component whose proportion is the greatest in the mixture.

The proportion of the host material of the formula (1) in the emitting layer is between 50.0 and 99.9% by weight, preferably between 80.0 and 99.5% by weight, particularly preferably between 90.0 and 99.0% by weight. Correspondingly, the proportion of the dopant in the emitting layer is between 0.1 and 50.0% by weight, preferably between 0.5 and 20.0% by weight, particularly preferably between 1.0 and 10.0% by weight.

Preferred dopants are selected from the class of the aromatic anthracenamines, the aromatic anthracenediamines, the aromatic pyrenamines, the aromatic pyrenediamines, the aromatic chrysenamines, the aromatic chrysenediamines, the monostyrylamines, the distyrylamines, the tristyrylamines, the tetrastyrylamines, the styrylphosphines, the styryl ethers and the arylamines. An aromatic anthracenamine is taken to mean a compound in which a diaryl amino group is bonded directly to an anthracene group, preferably in the 9-position. An aromatic anthracenediamine is taken to mean a compound in which two diaryl amino groups are bonded directly to an anthracene group, preferably in the 9,10-position. Aromatic pyrenamines and pyrenediamines or aromatic chrysenamines and chrysenediamines are defined analogously thereto. A monostyrylamine is taken to mean a compound which contains a styryl group and at least one, preferably aromatic amine. A distyrylamine is taken to mean a compound which contains two styryl groups and at least one, preferably aromatic amine. A tristyrylamine is taken to mean a compound which contains three styryl groups and at least one, preferably aromatic amine. A tetrastyrylamine is taken to mean a compound which contains four styryl groups and at least one,

preferably aromatic amine. Corresponding phosphines and ethers are defined analogously to the amines. For the purposes of this invention, an arylamine or an aromatic amine is taken to mean a compound which contains three aromatic or heteroaromatic ring systems bonded directly to the nitrogen. The styryl groups are particularly preferably stilbenes, which may also be further substituted. Particularly preferred dopants are selected from the classes of the tristilbenamines, the aromatic stilbenediamines, the anthracenediamines and the pyrenediamines. Very particularly preferred dopants are selected from the class of the tristyrylamines. Examples of dopants of this type are substituted or unsubstituted tristilbenamines or the dopants described in WO 06/000388, WO 06/058737 and WO 06/000389.

Preference is furthermore given to organic electroluminescent devices, characterised in that a plurality of emitting layers are used, where at least one of these layers comprises at least one compound of the formula (1). These emission layers particularly preferably have in total a plurality of emission maxima between 380 nm and 750 nm, resulting overall in white emission, i.e. at least one further emitting compound which is able to fluoresce or phosphoresce and emits yellow, orange or red light is also used in the further emitting layer(s). Particular preference is given to three-layer systems, where at least one of these layers comprises at least one compound of the formula (1) and where the three layers exhibit blue, green and orange or red emission (for the basic structure see, for example, WO 05/011013). Emitters which have broad-band emission bands and thus exhibit white emission are likewise suitable for white emission.

In addition to the compounds of the formula (1), further substances may also be present in the emitting layer, for example hole- or electron-transport materials.

If the symbol R stands for an $\text{N}(\text{Ar}^1)_2$ group and/or a substituent on the Ar group stands for an $\text{N}(\text{Ar}^1)_2$ group, the compound of the formula (1) is particularly suitable as emitting compound and/or as hole-transport material, as described in greater detail below.

If the compound of the formula (1) is employed as hole-transport material, it is preferably employed in a hole-transport layer and/or in a hole-injection layer. For the purposes of this invention, a hole-injection layer is a layer which is directly adjacent to the anode. For the purposes of this invention, a hole-transport layer is a layer which lies between a hole-injection layer and an emission layer. If the compounds of the formula (1) are used as hole-transport or hole-injection material, it may be preferred for them to be doped with electron-acceptor compounds, for example with $\text{F}_4\text{-TCNQ}$ or with compounds as described in EP 1476881 or EP 1596445.

If the compound of the formula (1) is employed as emitting compound, it is preferably employed in combination with a host material.

The proportion of the emitting compound of the formula (1) in the mixture of the emitting layer is between 0.1 and 50.0% by weight, preferably between 0.5 and 20.0% by weight, particularly preferably between 1.0 and 10.0% by weight. Correspondingly, the proportion of the host material in the layer is between 50.0 and 99.9% by weight, preferably between 80.0 and 99.5% by weight, particularly preferably between 90.0 and 99.0% by weight.

Suitable host materials are various classes of substance. Preferred host materials are selected from the classes of the oligoarylenes (for example 2, 2', 7, 7'-tetraphenylspirobifluorene as described in EP 676461 or dinaphthylanthracene), in particular oligoarylenes containing condensed aromatic groups, oligoarylenevinylenes (for example DPVBi or spiro-DPVBi as described in EP 676461), polypodal metal com-

plexes (for example as described in WO 04/081017), hole-conducting compounds (for example as described in WO 04/058911), electron-conducting compounds, in particular ketones, phosphine oxides, sulfoxides, etc. (for example as described in WO 05/084081 or WO 05/084082), atropisomers (for example as described in WO 06/048268) or boronic acid derivatives (for example as described in the unpublished application EP 05009643.7). Particularly preferred host materials are selected from the classes of the oligoarylenes containing naphthalene, anthracene and/or pyrene or atropisomers of these compounds, oligoarylenevinylenes, ketones, phosphine oxides and sulfoxides. Very particularly preferred host materials are selected from the classes of the oligoarylenes containing anthracene and/or pyrene or atropisomers of these compounds, phosphine oxides and sulfoxides.

Preference is furthermore given to an organic electroluminescent device, characterised in that one or more layers are coated by means of a sublimation method, where the materials are vapour-deposited in vacuum sublimation units at a pressure below 10^{-5} mbar, preferably below 10^{-6} mbar, particularly preferably below 10^{-7} mbar.

Preference is likewise given to an organic electroluminescent device, characterised in that one or more layers are coated by means of the OVPD (organic vapour phase deposition) method or with the aid of carrier-gas sublimation, where the materials are applied at a pressure between 10^{-5} mbar and 1 bar.

Preference is furthermore given to an organic electroluminescent device, characterised in that one or more layers are produced from solution, such as, for example, by spin coating, or by means of any desired printing process, such as, for example, screen printing, flexographic printing or offset printing, but particularly preferably LITI (light induced thermal imaging, thermotransfer printing) or ink-jet printing. Soluble compounds of the formula (1) are necessary for this purpose. The compounds according to the invention are therefore very highly suitable for processing from solution since they have high solubility in organic solvents due to the substitution.

The organic electroluminescent devices according to the invention have the following surprising advantages over the prior art:

1. The thermal stability and in particular the glass-transition temperature of the compounds becomes higher compared with compounds in accordance with the prior art which do not contain any trialkylsilyl groups while otherwise having the same structure.
2. The compounds according to the invention have very good solubility in common organic solvents, which simplifies the purification of the compounds during preparation and the cleaning of the vapour-deposition units (for example the shadow masks) and enables the compounds to be applied by solution processes.
3. The compounds according to the invention have higher hole and electron stability (redox stability) compared with comparable materials in accordance with the prior art which do not contain any $\text{Si}(\text{R}^2)_3$ groups.

The present application text is directed to the use of compounds according to the invention in relation to OLEDs and the corresponding displays.

In spite of this restriction of the description, it is possible for the person skilled in the art, without further inventive step, also to use the compounds according to the invention for further uses in other electronic devices, for example for organic field-effect transistors (O-FETs), organic thin-film transistors (O-TFTs), organic light-emitting transistors (O-LETs), organic integrated circuits (O-ICs), organic solar

cells (O-SCs), organic field-quench devices (O-FQDs), organic photoreceptors, light-emitting electrochemical cells (LECs) or organic laser diodes (O-lasers).

The present invention furthermore relates to the use of the compounds according to the invention in the corresponding devices and to these devices themselves.

The invention is explained in greater detail by the following examples without wishing it to be restricted thereby.

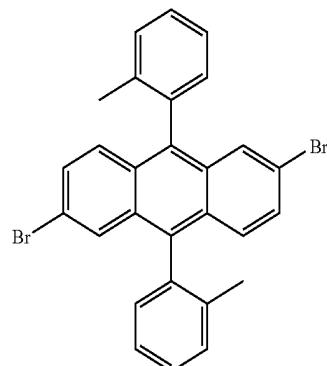
EXAMPLES

The following syntheses are carried out under a protective-gas atmosphere, unless indicated otherwise. The starting materials can be purchased from ALDRICH or ABCR (n-butyllithium, 2.5M in hexane, silanes, bromides, inorganics, solvents). 2,6-Dibromoanthraquinone is prepared as described by Lee et al., *Org. Lett.* 2005, 7(2), 323.

Example 1

2,6-Bis(trimethylsilyl)-9,10-bis(o-tolyl)anthracene

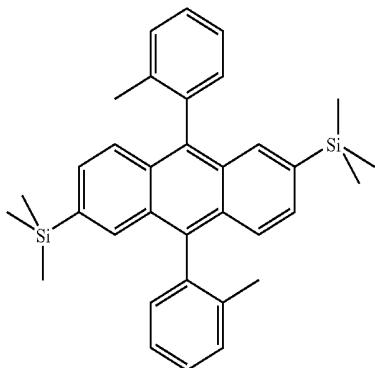
a) 2,6-Dibromo-9,10-bis(o-tolyl)anthracene



The corresponding organolithium reagent is prepared from 18.0 ml (150 mmol) of 2-bromotoluene in 500 ml of THF by addition of 60 ml of n-butyllithium (2.5M in hexane) at -78°C . and stirring for a further 1 h. 27.5 g (75 mmol) of 2,6-dibromoanthraquinone are added to this reagent. The reaction mixture is subsequently stirred at -78°C . for 1 h and warmed to room temperature over the course of 5 h, and a mixture of 100 ml of acetic acid and 200 ml of water is then added. The solid is filtered off with suction, washed with 200 ml of water, 100 ml of ethanol and twice with 200 ml of heptane each time and dried. The solid is refluxed for 3 h with 15.2 g (80 mmol) of tin(II) chloride (anhydrous) in 300 ml of DMF. After cooling, 500 ml of 2.5N hydrochloric acid are added, and the solid is filtered off with suction. The solid is washed three times with 100 ml of 2.5N hydrochloric acid each time, three times with 100 ml of water each time and three times with 100 ml of ethanol each time, dried under reduced pressure and recrystallised twice from DMF. Yield: 33.0 g (64 mmol), 85.2% of theory; purity: 99% according to HPLC.

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b) 2,6-Bis(trimethylsilyl)-9,10 bis(o-tolyl)anthracene

**42**

(2.5M in hexane) at -78°C . and stirring for a further 3 h, and 26.8 ml (210 mmol) of chlorotrimethylsilane are subsequently added. After the mixture has been stirred for a further 1 h and warmed to room temperature, the THF is removed under reduced pressure, the residue is taken up in 500 ml of dichloromethane, and the organic phase is washed three times with 500 ml of water each time, dried, filtered through Celite and freed from solvent under reduced pressure. The residue is recrystallised five times from toluene/acetonitrile and then sub-limed in a high vacuum, $p=1\times 10^{-5}$ mbar, $T=310^{\circ}\text{C}$. Yield: 23.6 g (47 mmol), 73.4% of theory; purity: 99.8% according to HPLC. Mixture of two atropisomers according to $^1\text{H-NMR}$ spectroscopy.

15

Example 2

Synthesis of Further Compounds According to the
Invention

The corresponding organolithium reagent is prepared from 33.0 g (64 mmol) of 2,6-dibromo-9,10-di-o-tolylanthracene in 500 ml of THF by addition of 77 ml of n-butyllithium

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The following compounds are prepared analogously to Example 1:

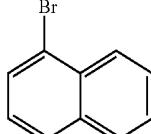
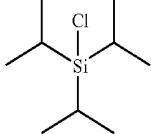
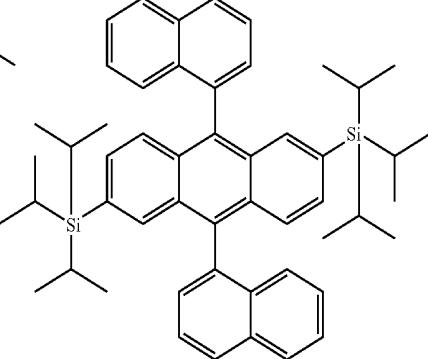
Ex.	Bromide/step a)	Silane/step b)	Product
3			
4			

-continued

Ex.	Bromide/step a)	Silane/step b)	Product
5			
6			
7			

-continued

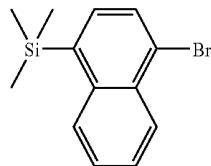
Ex.	Bromide/step a)	Silane/step b)	Product
8			
9			
10			

Ex.	Bromide/step a)	Silane/step b)	Product
11			

Example 12

9-(4-Methylnaphth-1-yl)-10-(4-trimethylsilylnaphthyl)-anthracene

a) Synthesis of (4-bromonaphth-1-yl)trimethylsilane



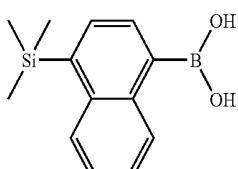
20 for 30 min., warmed to room temperature, then re-cooled to -78°C . and a mixture of 26.4 ml (234 mmol) of trimethyl borate in 50 ml of diethyl ether is added rapidly. After warming to -10°C ., the mixture is hydrolysed using 90 ml of 2N hydrochloric acid. The organic phase is separated off, washed 25 with water, dried over sodium sulfate and evaporated to dryness. The residue is taken up in 200 ml of n-heptane, and the colourless solid is filtered off with suction, washed with n-heptane and dried under reduced pressure. Yield: 26 g (106 mmol), 45% of theory; purity: 98% according to $^1\text{H-NMR}$.

30 c) Synthesis of 9-(4-methylnaphth-1-yl)-10-(4-trimethylsilylnaphthyl)-anthracene

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A solution of 114.38 g (400 mmol) of 1,4-dibromonaphthalene and 1 l of THF (absolute) is cooled to -78°C . under protective gas, 160 ml (400 mmol) of n-butyllithium (2.5M in n-hexane) are subsequently slowly added at this temperature, and the mixture is stirred at -78°C . for a further 30 h. A mixture of 52.3 ml (400 mmol) of chlorotrimethylsilane in 200 ml of THF (absolute) is added to the solution obtained in this way, and the mixture is slowly warmed to room temperature. After addition of 150 ml of EtOH and subsequently 300 ml of water, the organic phase is separated off, dried over magnesium sulfate and evaporated. The oil obtained in this way is distilled at 115–135° C. and 1.7 mbar, giving 80 g (286 mmol) (corresponding to 88% of theory) of the product having a purity of greater than 99.0% according to HPLC.

40 b) Synthesis of 4-(trimethylsilyl)naphth-1-ylboronic acid



45 1.78 g (5.6 mmol) of tri-o-tolylphosphine and 0.2 g (0.9 mmol) of palladium acetate are added to a vigorously stirred, degassed suspension of 22.8 g (93.3 mmol) of 4-trimethylsilylnaphth-1-ylboronic acid, 37.4 g (93.3 mmol) of 9-(4-methylnaphth-1-yl)anthracene and 90 g (230 mmol) of tripotassium phosphate in a mixture of 575 ml of water, 100 ml of dioxane and 860 ml of toluene, and the mixture is refluxed for 60 h. After cooling, the organic phase is separated off, washed three times with 200 ml of water and once with 200 ml of saturated aqueous sodium chloride solution and subsequently dried over magnesium sulfate. After the desiccant has been

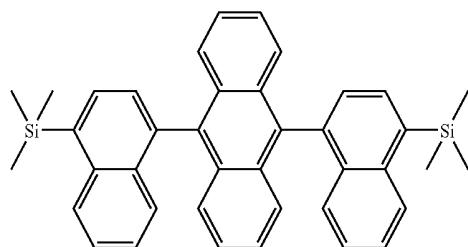
55 filtered off, the organic phase is evaporated to dryness under reduced pressure in a rotary evaporator. The grey residue obtained in this way is recrystallised from dioxane. The deposited crystals are filtered off with suction, washed with 50 ml of ethanol and subsequently dried under reduced pressure; yield: 38 g, 79% of theory; purity: 99.9% according to HPLC.

60 65 73.7 ml (184 mmol) of n-butyllithium (2.5M in hexane) are added dropwise to a solution, cooled to -78°C ., of 46.8 g (167.6 mmol) of (4-bromonaphth-1-yl)trimethylsilane in 950 ml of diethyl ether. The reaction mixture is stirred at -78°C .

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Example 13

9,10-Bis(4-trimethylsilylnaphthyl)anthracene

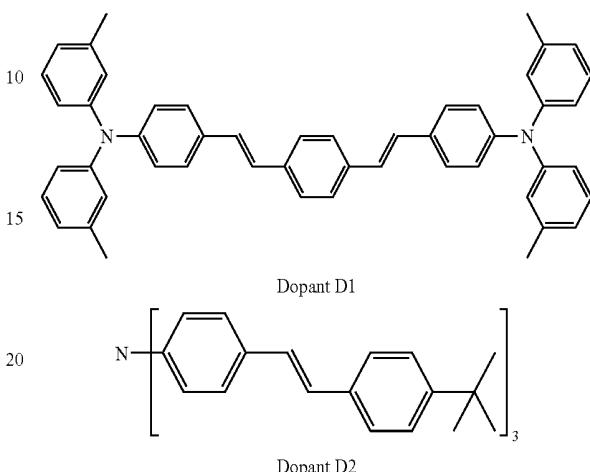


2.6 g (9.7 mmol) of tri-*o*-tolylphosphine and 0.365 g (1.63 mmol) of palladium acetate are added to a vigorously stirred, degassed suspension of 29.7 g (122 mmol) of 4-trimethylsilylnaphth-1-ylboronic acid (from Example 12b), 13.6 g (40.6 mmol) of 9,10-dibromoanthracene and 41 g (178 mmol) of tripotassium phosphate in a mixture of 163 ml of water, 200 ml of dioxane and 200 ml of toluene, and the mixture is refluxed for 60 h. After cooling, the organic phase is separated off, washed three times with 200 ml of water and once with 200 ml of saturated aqueous sodium chloride solution and subsequently dried over magnesium sulfate. After the desiccant has been filtered off, the organic phase is evaporated to dryness under reduced pressure in a rotary evaporator. The grey residue obtained in this way is recrystallised from dioxane. The deposited crystals are filtered off with suction, washed with 50 ml of ethanol and subsequently dried under reduced pressure; yield: 23 g, 78% of theory; purity: 99.9% according to HPLC.

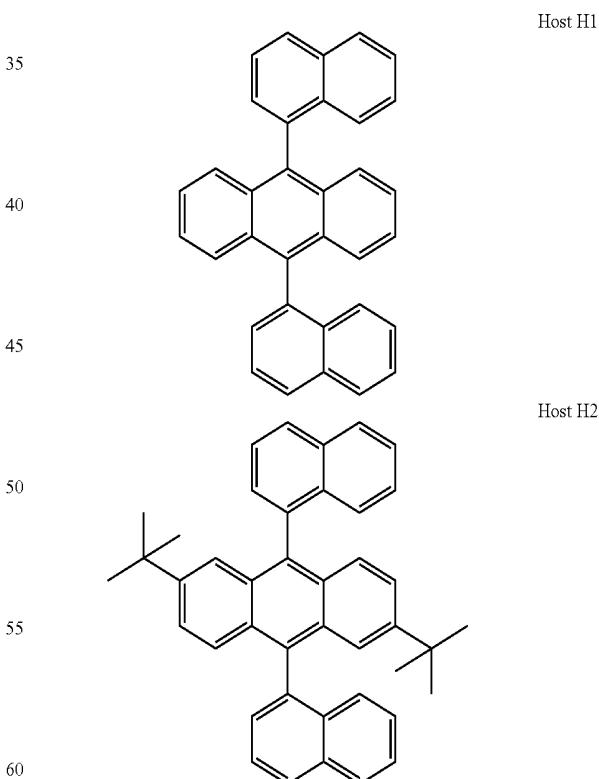
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Table 2 shows the results for some OLEDs (Examples 2 to 9) which comprise dopants D1, D2 and the compound from Example 8, where in each case the composition of the EML including the layer thicknesses is also given.

5 The structure of the dopants is depicted below:



The compounds from Examples 5, 10, 12 and 13 are employed as host material according to the invention. For comparison, host materials H1 and H2 are employed as host material in accordance with the prior art. The host materials are depicted below:



Hole-transport layer (HTL)	20 nm 2,2',7,7'-tetrakis(di- <i>para</i> -tolylamino)-spiro-9,9'-bifluorene (abbreviated to HTL-1)
Hole-transport layer (HTL)	20 nm NPB (N-naphthyl-N-phenyl-4,4'-di-aminobiphenyl)
Emission layer (EML)	see Table 1 for materials, concentration and layer thickness
Electron conductor (ETL)	20 nm AlQ ₃ (purchased from SynTec, tris(quinolinato)aluminium(III))
Cathode	1 nm LiF, 150 nm Al on top.

These OLEDs are characterised by standard methods; for this purpose, the electroluminescence spectral efficiency (measured in cd/A), the power efficiency (measured in lm/W) as a function of the brightness, calculated from current/voltage/brightness characteristic lines (IUL characteristic lines), and the lifetime are determined. The lifetime is defined as the time after which the initial brightness of 1000 cd/m² has dropped to half.

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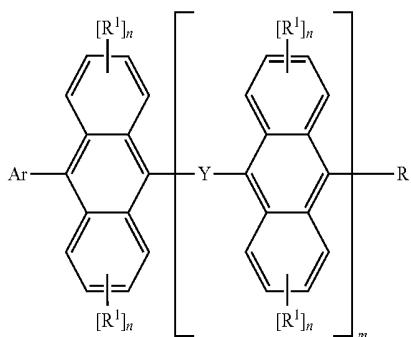
As can be seen from the examples in Table 2, the electroluminescent devices according to the invention exhibit higher efficiency and a longer lifetime with comparable colour coordinates compared with electroluminescent devices in accordance with the prior art.

TABLE 2

Example	EML	Max. efficiency (cd/A)	Voltage (V) at 100 cd/m ²	CIE	Lifetime (h)
Example 15	H1: D1 (3%) (comparison) (30 nm)	11.8	5.5	x = 0.17; y = 0.32	6700
Example 16	H1: D1 (5%) (comparison) (30 nm)	12.2	5.3	x = 0.17; y = 0.33	7000
Example 17	H1: D1 (7%) (comparison) (30 nm)	11.5	5.2	x = 0.18; y = 0.36	5300
Example 18	H2: D1 (5%) (comparison) (30 nm)	11.8	5.0	x = 0.17; y = 0.35	7800
Example 19	Example 13: D1 (3%) (30 nm)	11.0	5.4	x = 0.17; y = 0.33	7200
Example 20	Example 13: D1 (5%) (30 nm)	12.4	5.2	x = 0.17; y = 0.35	7900
Example 21	Example 12: D1 (3%) (30 nm)	11.8	5.3	x = 0.17; y = 0.32	8000
Example 22	Example 12: D1 (5%) (30 nm)	12.8	5.1	x = 0.17; y = 0.32	8500
Example 23	Example 10: D1 (5%) (30 nm)	13	4.8	x = 0.18; y = 0.37	8800
Example 24	Example 5: D1 (5%) (30 nm)	12.8	5.0	x = 0.17; y = 0.35	8400
Example 25	H1: D2 (5%) (comparison) (30 nm)	4.2	5.1	x = 0.15; y = 0.11	1600
Example 26	Example 10: D2 (5%) (30 nm)	5.1	5.1	x = 0.15; y = 0.14	2200
Example 27	Example 12: D2 (5%) (30 nm)	4.5	5.0	x = 0.15; y = 0.12	3000
Example 28	H1: Example 8 (5%) (30 nm)	6.1	5.1	x = 0.15; y = 0.17	4000
Example 29	Example 12: Example 8 (5%) (30 nm)	6.2	4.8	x = 0.15; y = 0.16	4500

The invention claimed is:

1. An organic electronic device comprising at least one silyl-substituted compound represented by formula (1)



Formula (1)

wherein the two radicals Ar¹ are optionally connected to one another by a single bond or an O, S, N(R¹), or C(R¹)₂ group;

R is an aromatic or heteroaromatic ring system having 5 to 40 aromatic ring atom sand optionally substituted by one or more radicals R¹ or an N(Ar¹)₂ group, where the two radicals Ar¹ are optionally connected to one another by a single bond or an O, S, N(R¹), or C(R¹)₂ group;

Ar¹ is, identically or differently on each occurrence, an aromatic or heteroaromatic ring system having 5 to 40 aromatic ring atoms and optionally substituted by one or more radicals R¹;

Y is, identically or differently on each occurrence, a divalent group containing up to 40 C atoms, —O—, —S—, —NR¹—, —P(=O)R¹—, or a single bond;

R¹ is, identically or differently on each occurrence, Si(R²)₃; F; Cl; Br; I; CN; N(R³)₂; NO₂; a straight-chain alkyl, alkoxy or thioalkoxy group having 1 to 40 C atoms and optionally substituted by one or more radicals R³, wherein one or more non-adjacent CH₂ groups are optionally replaced by —R₃C=CR₃—, —C—C—, Si(R³)₂, Ge(R³)₂, Sn(R³)₂, C=O, C=S, C=Se, C=NR³, —O—, —S—, —N(R³)—, or —CONR³— and wherein one or more H atoms are optionally replaced by F, Cl, Br, I, CN, or NO₂; a branched or cyclic alkyl, alkoxy or thioalkoxy group

wherein

Ar is a 1-naphthyl group or a 9-anthryl group, each optionally substituted by one or more radicals R¹ and/or one or more radicals N(Ar¹)₂, wherein one or two carbon atoms of said 1-naphthyl group or said 9-anthryl group is optionally replaced by N, and

having 3 to 40 C atoms and optionally substituted by one or more radicals R^3 , wherein one or more non-adjacent CH_2 groups are optionally replaced by $-R_3C=CR_3-$, $-C\equiv C-$, $Si(R^3)_2$, $Ge(R^3)_2$, $Sn(R^3)_2$, $C=O$, $C=S$, $C=Se$, $C=NR_3$, $-O-$, $-S-$, $-N(R_3)-$, or $-CONR_3-$ and wherein one or more H atoms are optionally replaced by F, Cl, Br, I, CN, or NO_2 ; an aryl or heteroaryl group having 5 to 24 aromatic ring atoms and optionally substituted by one or more radicals R_3 ; or an aryloxy or heteroaryloxy group having 5 to 24 aromatic ring atoms and optionally substituted by one or more radicals R_3 ; or a combination of two, three, four or five of these systems; and wherein two or more adjacent substituents R^1 optionally define a mono- or polycyclic, aliphatic ring system with one another;

R^2 is, identically or differently on each occurrence, a straight-chain alkyl group having up to 40 C atoms and optionally substituted by an aryl or heteroaryl group having 5 to 24 aromatic ring atoms optionally substituted by one or more radicals R^3 or an aryloxy or heteroaryloxy group having 5 to 24 aromatic ring atoms optionally substituted by one or more radicals R^3 ; wherein one or more non-adjacent CH_2 groups which are not bonded directly to silicon are optionally replaced by $-R_3C=CR_3-$, $-C\equiv C-$, $Si(R^3)_2$, $Ge(R^3)_2$, $Sn(R^3)_2$, $C=O$, $C=S$, $C=Se$, $C=NR^3$, $-O-$, $-S-$, $-N(R^3)-$, or $-CONR^3-$, and wherein one or more H atoms is optionally replaced by F, Cl, Br, I, CN, or NO_2 ; a branched or cyclic alkyl group having 3 to 40 C atoms optionally substituted by an aryl or heteroaryl group having 5 to 24 aromatic ring atoms optionally substituted by one or more radicals R^3 or an aryloxy or heteroaryloxy group having 5 to 24 aromatic ring atoms optionally substituted by one or more radicals R^3 , wherein one or more non-adjacent CH_2 groups which are not bonded directly to silicon are optionally replaced by $-R^3C=CR^3-$, $-C\equiv C-$, $Si(R^3)_2Ge(R^3)_2$, $(R^3)_2$, $C=O$, $C=S$, $C=Se$, $C=NR^3$, $-O-$, $-S-$, $-N(R^3)-$, or $-CONR^3-$, and wherein one or more H atoms is optionally replaced by F, Cl, Br, I, CN, or NO_2 ; and wherein two or more substituents R^2 optionally define a mono- or polycyclic ring system with one another; R^3 is, identically or differently on each occurrence, H or a hydrocarbon radical having up to 20 C atoms, which may be aliphatic or aromatic or a combination of aliphatic and aromatic and is optionally substituted by F; and wherein two or more radicals R^3 optionally define a mono- or polycyclic, aliphatic or aromatic ring system with one another;

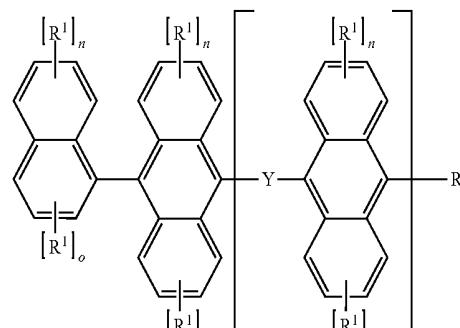
n is, identically or differently on each occurrence, 0, 1, 2, 3, or 4; and

m is 0, 1, 2, 3, 4, or 5;

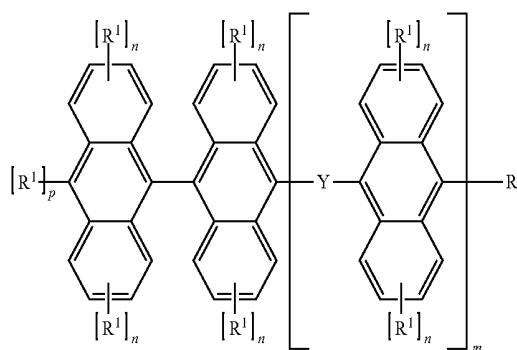
with the proviso that at least one radical R^1 which is an $Si(R^2)_3$ group is present and is bonded to the central anthracene unit in the 2-position and/or in the 6-position, and/or, when Ar is 1-naphthyl, is bonded to the 1-naphthyl group in the 4-position and, when Ar is 9-anthyl, is bonded to the 9-anthryl group in the 10-position, and/or is bonded to the R group.

2. The organic electronic device of claim 1, wherein the silyl-substituted compound is represented by formula (1a), (1b), (1c), or (1d):

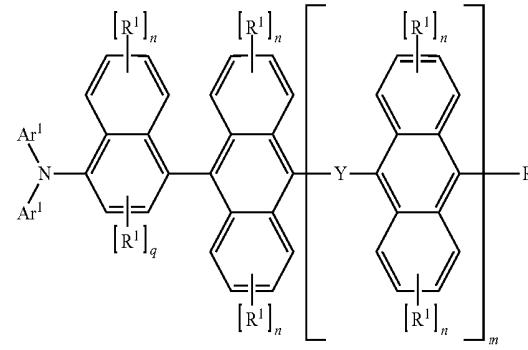
Formula (1a)



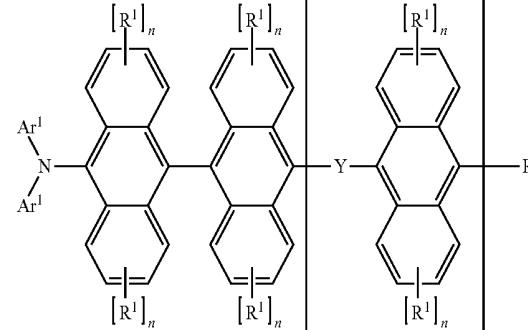
Formula (1b)



Formula (1c)



Formula (1d)



wherein

the two radicals Ar^1 are optionally connected to one another by a single bond or an O, S, $N(R^1)$, or $C(R^1)_2$ group;

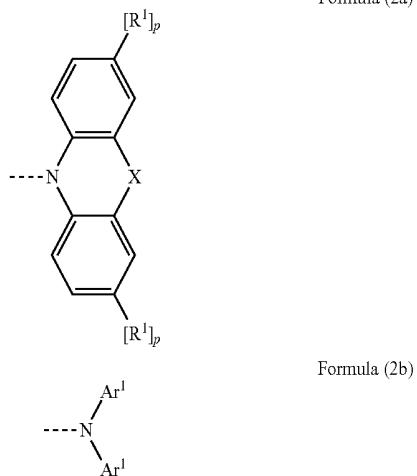
o is 0, 1, 2, or 3;

p is 0 or 1; and

q is 0, 1 or 2.

3. The organic electronic device of claim 2 comprising the silyl-substituted compound wherein p is 1.

4. The organic electronic device of claim 1 comprising the silyl-substituted compound, wherein R is an aromatic or heteroaromatic ring system having 6 to 24 aromatic ring atoms and optionally substituted by one or more radicals R¹; or is a group of formula (2a) or (2b)



wherein

X is a single bond, O, S, N(R¹), or C(R¹)₂;

Ar¹ is, identically or differently on each occurrence, an aryl or heteroaryl group having 5 to 20 aromatic ring atoms and optionally substituted by one or more radicals R¹.

5. The organic electronic device of claim 4 comprising the silyl-substituted compound, wherein said aryl or heteroaryl group has 6 to 14 aromatic ring atoms and is optionally substituted by one or more radicals R¹.

6. The organic electronic device of claim 5 comprising the silyl-substituted compound, wherein said aryl or heteroaryl group is phenyl, 1-naphthyl, or 2-naphthyl, each of which is optionally substituted by one or more radicals R¹.

7. The organic electronic device of claim 1 comprising the silyl-substituted compound, wherein R is a condensed aryl or heteroaryl group having 10 to 16 aromatic ring atoms or an aromatic, optionally bridged biaryl group, each of which is optionally substituted by one or more radicals R¹.

8. The organic electronic device of claim 7 comprising the silyl-substituted compound wherein R is a 1-naphthyl, 2-naphthyl, 9-anthryl, 2-phenanthrenyl, 9-phenanthrenyl, quinolinyl, isoquinolinyl, ortho-biphenyl, meta-biphenyl, para-biphenyl, 2-fluorenyl, or 2-spirobifluorenyl group, each of which is optionally substituted by one or more radicals R¹.

9. The organic electronic device of claim 1 comprising the silyl-substituted compound wherein R1 is, identically or differently on each occurrence, Si(R²)₃; F; a straight-chain alkyl or alkoxy group having up to 6 C atoms wherein one or more CH₂ groups is optionally replaced by —R³C=C R³—, Si(R³)₂, —O—, —S—, or —N(R³)— and wherein one or more H atoms is optionally replaced by F; a branched or cyclic alkyl or alkoxy group having 3 to 10 C atoms, wherein one or more CH₂ groups is optionally replaced by —R³C=C R³—, Si(R³)₂, —O—, —S—, or —N(R³)— and wherein one or more H atoms is optionally replaced by F; or an aryl or heteroaryl group having 5 to 14 aromatic ring atoms and optionally substituted by one or more radicals R³; or a combination of two or three of these systems; and wherein two or more radicals R¹ optionally define a mono- or polycyclic, aliphatic ring system with one another.

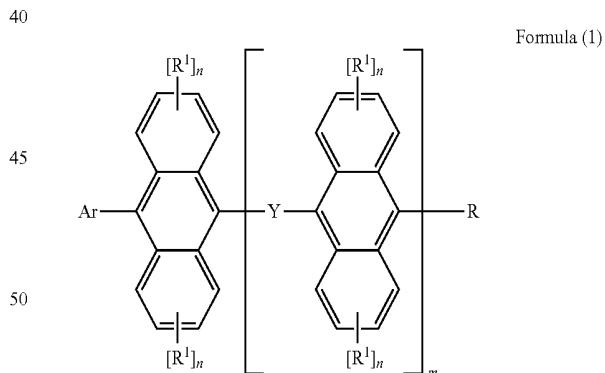
10. The organic electronic device of claim 1 comprising the silyl-substituted compound wherein Y is, identically or differently on each occurrence, a linear alkylene group having up to 10 C atoms, a branched or cyclic alkylene or alkylidene group having 3 to 10 C atoms, a divalent aromatic group having 6 to 25 C atoms, C=O, —O—, —S—, —N(R¹)—, —P(=O)R¹—, or a single bond.

11. The organic electronic device of claim 1 comprising the silyl-substituted compound wherein it contains one, two, three, or four groups of formula Si(R²)₃.

12. The organic electronic device of claim 1 comprising the silyl-substituted compound wherein R² of Si(R²)₃ is selected from the group consisting of straight-chain alkyl groups having up to 10 C atoms, wherein one or more non-adjacent CH₂ groups which are not bonded directly to the silicon are optionally replaced by O and wherein one or more H atoms is optionally replaced by F, and branched or cyclic alkyl groups having 3 to 10 C atoms, wherein one or more non-adjacent CH₂ groups which are not bonded directly to the silicon are optionally replaced by O and wherein one or more H atoms is optionally replaced by F; and wherein two or more substituents R² optionally define a mono- or polycyclic ring system with one another.

13. The organic electronic device of claim 1, wherein said device is selected from the group consisting of organic electroluminescent devices, organic field-effect transistors, organic thin-film transistors, organic light-emitting transistors, organic integrated circuits, organic solar cells, organic field-quench devices, organic photoreceptors, light-emitting electrochemical cells, and organic laser diodes.

14. The organic electronic device of claim 1, wherein said device is an organic electroluminescent device comprising at least one emitting layer, hole-transport layer, hole-injection layer, hole-blocking layer, and/or electron-transport layer, wherein at least one of said layers comprises at least one silyl-substituted compound of formula (1)



wherein

Ar is a 1-naphthyl group or a 9-anthryl group, each optionally substituted by one or more radicals R¹ and/or one or more radicals N(Ar¹)₂, wherein one or two carbon atoms of said 1-naphthyl group or said 9-anthryl group is optionally replaced by N, and wherein the two radicals Ar¹ are optionally connected to one another by a single bond or an O, S, N(R¹), or C(R¹)₂ group;

R is an aromatic or heteroaromatic ring system having 5 to 40 aromatic ring atoms and optionally substituted by one or more radicals R¹ or an N(Ar¹)₂ group, where the two radicals Ar¹ are optionally connected to one another by a single bond or an O, S, N(R¹), or C(R¹)₂ group;

Ar¹ is, identically or differently on each occurrence, an aromatic or heteroaromatic ring system having 5 to 40 aromatic ring atoms and optionally substituted by one or more radicals R¹;

Y is, identically or differently on each occurrence, a divalent group containing up to 40 C atoms, —O—, —S—, —NR¹—, —P(=O)R1-, or a single bond;

R¹ is, identically or differently on each occurrence, Si(R²)₃; F; Cl; Br; I; CN; N(R²)₃; NO₂; a straight-chain alkyl, alkoxy or thioalkoxy group having 1 to 40 C atoms and optionally substituted by one or more radicals R³, wherein one or more non-adjacent CH₂ groups are optionally replaced by —R³C=CR³—, —C≡C—, Si(R³)₂, Ge(R²)₃, Sn(R²)₃, C=O, C=S, C=Se, C=NR³, —O—, —S—, —N(R³)—, or —CONR³— and wherein one or more H atoms are optionally replaced by F, Cl, Br, I, CN, or NO₂; a branched or cyclic alkyl, alkoxy or thioalkoxy group having 3 to 40 C atoms and optionally substituted by one or more radicals R³, wherein one or more non-adjacent CH₂ groups are optionally replaced by —R³C=CR³—, —C≡C—, Si(R²)₃, Ge(R²)₃, Sn(R²)₃, C=O, C=S, C=Se, C=NR³, —O—, —S—, —N(R³)—, or —CONR³— and wherein one or more H atoms are optionally replaced by F, Cl, Br, I, CN, or NO₂; an aryl or heteroaryl group having 5 to 24 aromatic ring atoms and optionally substituted by one or more radicals R³; or an aryloxy or heteroaryloxy group having 5 to 24 aromatic ring atoms and optionally substituted by one or more radicals R³; or a combination of two, three, four or five of these systems; and wherein two or more adjacent substituents R¹ optionally define a mono- or polycyclic, aliphatic ring system with one another;

R² is, identically or differently on each occurrence, a straight-chain alkyl group having up to 40 C atoms and optionally substituted by an aryl or heteroaryl group having 5 to 24 aromatic ring atoms optionally substituted by one or more radicals R³ or an aryloxy or heteroaryloxy group having 5 to 24 aromatic ring atoms optionally substituted by one or more radicals R³; wherein one or more non-adjacent CH₂ groups which are not bonded directly to silicon are optionally replaced by —R³C=CR³—, —C≡C—, Si(R²)₃, Ge(R²)₃, Sn(R²)₃, C=O, C=S, C=Se, C=NR³, —O—, —S—, —N(R³)—, or —CONR³—, and wherein one or more H atoms is optionally replaced by F, Cl, Br, I, CN, or NO₂; a branched or cyclic alkyl group having 3 to 40 C atoms optionally substituted by an aryl or heteroaryl group having 5 to 24 aromatic ring atoms optionally substituted by one or more radicals R³ or an aryloxy or heteroaryloxy group having 5 to 24 aromatic ring atoms optionally substituted by one or more radicals R³, wherein one or more non-adjacent CH₂ groups which are not bonded directly to silicon are optionally adjacent CH₂ groups are optionally replaced by —R³C=CR³—, —C≡C—, Si(R²)₃, Ge(R²)₃, Sn(R²)₃, C=O, C=S, C=Se, C=NR³, —O—, —S—, —N(R³)—, or

—CONR³— and wherein one or more H atoms are optionally replaced by F, Cl, Br, I, CN, or NO₂; a branched or cyclic alkyl, alkoxy or thioalkoxy group having 3 to 40 C atoms and optionally substituted by one or more radicals R³, wherein one or more non-adjacent CH₂ groups are optionally replaced by —R³C=CR³—, C≡C—, Si(R²)₃, Ge(R²)₃, Sn(R²)₃, C=O, C=S, C=Se, C=NR³, —O—, —S—, —N(R³)—, or —CONR³— and wherein one or more H atoms are optionally replaced by F, Cl, Br, I, CN, or NO₂; an aryl or heteroaryl group having 5 to 24 aromatic ring atoms and optionally substituted by one or more radicals R³; or an aryloxy or heteroaryloxy group having 5 to 24 aromatic ring atoms and optionally substituted by one or more radicals R³; or a combination of two, three, four or five of these systems; and wherein two or more adjacent substituents R¹ optionally define a mono- or polycyclic, aliphatic ring system with one another;

R³ is, identically or differently on each occurrence, H or a hydrocarbon radical having up to 20 C atoms, which may be aliphatic or aromatic or a combination of aliphatic and aromatic and is optionally substituted by F; and wherein two or more radicals R³ optionally define a mono- or polycyclic, aliphatic or aromatic ring system with one another;

n is, identically or differently on each occurrence, 0, 1, 2, 3, or 4; and

m is 0, 1, 2, 3, 4, or 5;

wherein at least one radical R¹ which represents a Si(R²)₃ group is present.

15. The organic electronic device of claim 14, wherein said at least one silyl-substituted compound of formula (1) is employed as host material for fluorescent emitters and/or as electron-transport material and/or as hole-blocking material when R is an aromatic or heteroaromatic ring system.

16. The organic electronic device of claim 14, wherein said at least one silyl-substituted compound of formula (1) is employed as emitting compound and/or as hole-transport material when R is N(Ar¹)₂.

17. The organic electronic device of claim 1 comprising the silyl-substituted compound wherein R² is a straight-chain alkyl group having 1 to 4 C atoms or a branched alkyl group having 3 or 4 C atoms, wherein said straight-chain and branched alkyl groups are optionally substituted with fluorine atoms.

18. The organic electronic device of claim 1 comprising the silyl-substituted compound wherein R² is selected from the group consisting of methyl, CF₃, ethyl, isopropyl, and tert-butyl.

19. The organic electronic device of claim 1 comprising the silyl-substituted compound wherein Si(R²)₃ is selected from the group consisting of Si(Me)₃, Si(Me)₂(t-Bu), SiMe(t-Bu)₂, and Si(i-Pr)₃.

20. The organic electronic device of claim 1 comprising the silyl-substituted compound, wherein Ar and R are identical.

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申请(专利权)人(译)	MERCK PATENT GMBH		
当前申请(专利权)人(译)	MERCK PATENT GMBH		
[标]发明人	HEIL HOLGER STOESSEL PHILIPP PARHAM AMIR VESTWEBER HORST		
发明人	HEIL, HOLGER STOESSEL, PHILIPP PARHAM, AMIR VESTWEBER, HORST		
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摘要(译)

本发明涉及蒽衍生物，其在有机电致发光器件中的用途，以及包含这些化合物的有机电致发光器件。

Formula (1)

